MCP6N11

500 kHz, 800 µA Instrumentation Amplifier

Features

- Rail-to-Rail Input and Output
- Gain Set by 2 External Resistors
- Minimum Gain (G_{MIN}) Options:
  1, 2, 5, 10 or 100 V/V
- Common Mode Rejection Ratio (CMRR): 115 dB (typical, G_{MIN} = 100)
- Power Supply Rejection Ratio (PSRR): 112 dB (typical, G_{MIN} = 100)
- Bandwidth: 500 kHz (typical, Gain = G_{MIN})
- Supply Current: 800 µA/channel (typical)
- Single Channel
- Enable/V_{OS} Calibration pin: (EN/$\overline{CAL}$)
- Power Supply: 1.8V to 5.5V
- Extended Temperature Range: -40°C to +125°C

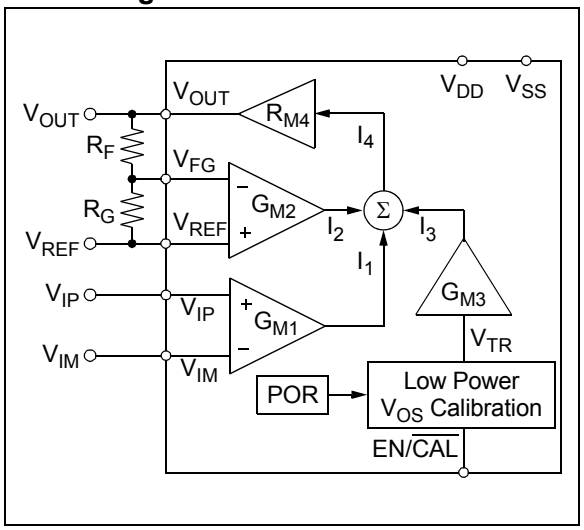
Typical Applications

- High Side Current Sensor
- Wheatstone Bridge Sensors
- Difference Amplifier with Level Shifting
- Power Control Loops

Design Aids

- Microchip Advanced Part Selector (MAPS)
- Demonstration Board
- Application Notes

Block Diagram



Description

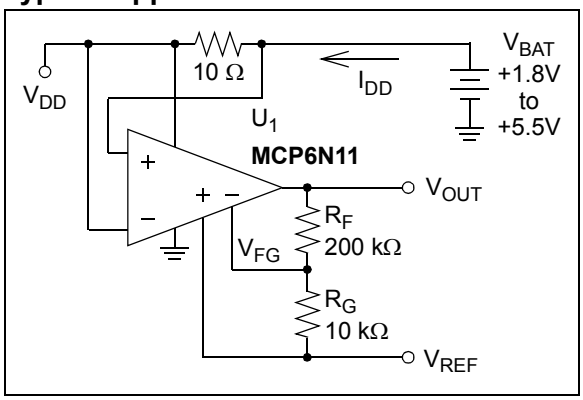
Microchip Technology Inc. offers the single MCP6N11 instrumentation amplifier (INA) with Enable/V_{OS} Calibration pin (EN/$\overline{CAL}$) and several minimum gain options. It is optimized for single-supply operation with rail-to-rail input (no common mode crossover distortion) and output performance.

Two external resistors set the gain, minimizing gain error and drift-over temperature. The reference voltage (V_{REF}) shifts the output voltage (V_{OUT}).

The supply voltage range (1.8V to 5.5V) is low enough to support many portable applications. All devices are fully specified from -40°C to +125°C.

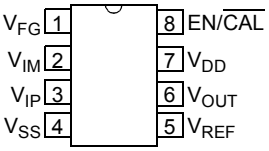
These parts have five minimum gain options (1, 2, 5, 10 and 100 V/V). This allows the user to optimize the input offset voltage and input noise for different applications.

Typical Application Circuit

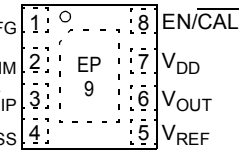


Package Types

MCP6N11
SOIC



MCP6N11
2×3 TDFN *



* Includes Exposed Thermal Pad (EP); see Table 3-1.

Minimum Gain Options

Table 1 shows key specifications that differentiate between the different minimum gain (G_{MIN}) options. See **Section 1.0 "Electrical Characteristics"**, **Section 6.0 "Packaging Information"** and **Product Identification System** for further information on G_{MIN}.

TABLE 1: KEY DIFFERENTIATING SPECIFICATIONS

Part No.	G_{MIN} (V/V) Nom.	V_{OS} (±mV) Max.	$\Delta V_{OS}/\Delta T_A$ (±µV/°C) Typ.	CMRR (dB) Min. V_{DD} = 5.5V	PSRR (dB) Min.	V_{DMH} (V) Max.	GBWP (MHz) Nom.	E_{ni} (μV_{P-P}) Nom. (f = 0.1 to 10 Hz)	e_{ni} (nV/√Hz) Nom. (f = 10 kHz)
MCP6N11-001	1	3.0	90	70	62	2.70	0.50	570	950
MCP6N11-002	2	2.0	45	78	68	1.35	1.0	285	475
MCP6N11-005	5	0.85	18	80	75	0.54	2.5	114	190
MCP6N11-010	10	0.50	9.0	81	81	0.27	5.0	57	95
MCP6N11-100	100	0.35	2.7	88	86	0.027	35	18	35

1.0 ELECTRICAL CHARACTERISTICS

1.1 Absolute Maximum Ratings †

$V_{DD} - V_{SS}$ 6.5V
Current at Input Pins †† .....±2 mA
Analog Inputs (V_{IP} and V_{IM}) †† ..... V_{SS} – 1.0V to V_{DD} + 1.0V
All Other Inputs and Outputs ..... V_{SS} – 0.3V to V_{DD} + 0.3V
Difference Input Voltage..... $|V_{DD} - V_{SS}|$
Output Short Circuit Current .....Continuous
Current at Output and Supply Pins .....±30 mA
Storage Temperature .....-65°C to +150°C
Max. Junction Temperature .....+150°C
ESD protection on all pins (HBM, CDM, MM).≥ 2 kV, 1.5 kV, 300V

† Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

†† See **Section 4.2.1.2 "Input Voltage Limits"** and **Section 4.2.1.3 "Input Current Limits"**.

1.2 Specifications

TABLE 1-1: DC ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

Parameters	Sym	Min	Typ	Max	Units	G_{MIN}	Conditions
Input Offset							
Input Offset Voltage, Calibrated	V_{OS}	-3.0	—	+3.0	mV	1	**(Note 2)**
		-2.0	—	+2.0	mV	2	
		-0.85	—	+0.85	mV	5	
		-0.50	—	+0.50	mV	10	
		-0.35	—	+0.35	mV	100	
Input Offset Voltage Trim Step	V_{OSTRM}	—	0.36	—	mV	1	
		—	0.21	—	mV	2	
		—	0.077	—	mV	5	
		—	0.045	—	mV	10	
		—	0.014	—	mV	100	
Input Offset Voltage Drift	$\Delta V_{OS}/\Delta T_A$	—	$\pm 90/G_{MIN}$	—	µV/°C	1 to 10	T_A= -40°C to +125°C **(Note 3)**
		—	±2.7	—	µV/°C	100	
Power Supply Rejection Ratio	PSRR	62	82	—	dB	1	
		68	88	—	dB	2	
		75	96	—	dB	5	
		81	102	—	dB	10	
		86	112	—	dB	100	

Note 1: $V_{CM} = (V_{IP} + V_{IM}) / 2$, $V_{DM} = (V_{IP} - V_{IM})$ and $G_{DM} = 1 + R_F/R_G$.
2: The V_{OS} spec limits include 1/f noise effects.
3: This is the input offset drift without V_{OS} re-calibration; toggle EN/$\overline{CAL}$ to minimize this effect.
4: These specs apply to both the V_{IP}, V_{IM} input pair (use V_{CM}) and to the V_{REF}, V_{FG} input pair (V_{REF} takes V_{CM}'s place).
5: This spec applies to the V_{IP}, V_{IM}, V_{REF} and V_{FG} pins individually.
6: Figure 2-11 and Figure 2-19 show the V_{IVR} and V_{DMR} variation over temperature.
7: See **Section 1.5 "Explanation of DC Error Specs"**.

TABLE 1-1: DC ELECTRICAL SPECIFICATIONS (CONTINUED)

Electrical Characteristics: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = $V_{DD}/2$, V_{DM} = 0V, V_{REF} = $V_{DD}/2$, V_L = $V_{DD}/2$, R_L = 10 kΩ to V_L and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

Parameters	Sym	Min	Typ	Max	Units	G_{MIN}	Conditions
Input Current and Impedance (Note 4)							
Input Bias Current	I_B	—	10	—	pA	all	
Across Temperature		—	80	—	pA		T_A= +85°C
Across Temperature		0	2	5	nA		T_A= +125°C
Input Offset Current	I_{OS}	—	±1	—	pA		
Across Temperature		—	±5	—	pA		T_A= +85°C
Across Temperature		-1	±0.05	+1	nA		T_A= +125°C
Common Mode Input Impedance	Z_{CM}	—	10^{13}||6	—	Ω||pF		
Differential Input Impedance	Z_{DIFF}	—	10^{13}||3	—	Ω||pF		
Input Common Mode Voltage (V_{CM} or V_{REF}) (Note 4)							
Input Voltage Range	V_{IVL}	—	—	V_{SS} – 0.2	V	all	**(Note 5, Note 6)**
	V_{IVH}	V_{DD} + 0.15	—	—	V		
Common Mode Rejection Ratio	CMRR	62	79	—	dB	1	V_{CM} = V_{IVL} to V_{IVH}, V_{DD} = 1.8V
		69	87	—	dB	2	
		75	101	—	dB	5	
		79	107	—	dB	10	
		86	119	—	dB	100	
		70	94	—	dB	1	V_{CM} = V_{IVL} to V_{IVH}, V_{DD} = 5.5V
		78	100	—	dB	2	
		80	108	—	dB	5	
		81	114	—	dB	10	
		88	115	—	dB	100	
Common Mode Non-Linearity	INL_{CM}	-1000	±115	+1000	ppm	1	V_{CM} = V_{IVL} to V_{IVH}, V_{DM} = 0V, V_{DD} = 1.8V **(Note 7)**
		-570	±27	+570	ppm	2	
		-230	±11	+230	ppm	5	
		-125	±6	+125	ppm	10	
		-50	±2	+50	ppm	100	
		-400	±42	+400	ppm	1	V_{CM} = V_{IVL} to V_{IVH}, V_{DM} = 0V, V_{DD} = 5.5V **(Note 7)**
		-220	±10	+220	ppm	2	
		-100	±4	+100	ppm	5	
		-50	±2	+50	ppm	10	
		-30	±1	+30	ppm	100	

Note 1: V_{CM} = (V_{IP} + V_{IM}) / 2, V_{DM} = (V_{IP} – V_{IM}) and G_{DM} = 1 + R_F/R_G.
2: The V_{OS} spec limits include 1/f noise effects.
3: This is the input offset drift without V_{OS} re-calibration; toggle EN/$\overline{CAL}$ to minimize this effect.
4: These specs apply to both the V_{IP}, V_{IM} input pair (use V_{CM}) and to the V_{REF}, V_{FG} input pair (V_{REF} takes V_{CM}'s place).
5: This spec applies to the V_{IP}, V_{IM}, V_{REF} and V_{FG} pins individually.
6: Figure 2-11 and Figure 2-19 show the V_{IVR} and V_{DMR} variation over temperature.
7: See **Section 1.5 "Explanation of DC Error Specs"**.

TABLE 1-1: DC ELECTRICAL SPECIFICATIONS (CONTINUED)

Electrical Characteristics: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

Parameters	Sym	Min	Typ	Max	Units	G_{MIN}	Conditions
Input Differential Mode Voltage (V_{DM}) (Note 4)							
Differential Input Voltage Range	V_{DML}	-2.7/G_{MIN}	—	—	V	all	V_{REF} = (V_{DD} – $G_{DM}V_{DM}$)/2 **(Note 6)**
	V_{DMH}	—	—	+2.7/G_{MIN}	V		
Differential Gain Error	g_E	-1	±0.13	+1	%		V_{DM} = V_{DML} to V_{DMH}, V_{REF} = (V_{DD} – $G_{DM}V_{DM}$)/2
Differential Gain Drift	$\Delta g_E/\Delta T_A$	—	±0.0006	—	%/°C		
Differential Non-Linearity	INL_{DM}	-500	±30	+500	ppm	1	**(Note 7)**
		-800	±40	+800	ppm	2, 5	
		-2000	±100	+2000	ppm	10, 100	
DC Open-Loop Gain	A_{OL}	61	84	—	dB	1	V_{DD} = 1.8V, V_{OUT} = 0.2V to 1.6V
		68	90	—	dB	2	
		76	98	—	dB	5	
		78	104	—	dB	10	
		86	116	—	dB	100	
		70	94	—	dB	1	V_{DD} = 5.5V, V_{OUT} = 0.2V to 5.3V
		77	100	—	dB	2	
		84	108	—	dB	5	
		90	114	—	dB	10	
		97	125	—	dB	100	
Output							
Minimum Output Voltage Swing	V_{OL}	—	—	V_{SS} + 15	mV	all	V_{DM} = -V_{DD}/(2G_{DM}), V_{DD} = 1.8V, V_{REF} = V_{DD}/2 – 1V
		—	—	V_{SS} + 25	mV		V_{DM} = -V_{DD}/(2G_{DM}), V_{DD} = 5.5V, V_{REF} = V_{DD}/2 – 1V
Maximum Output Voltage Swing	V_{OH}	V_{DD} – 15	—	—	mV		V_{DM} = V_{DD}/(2G_{DM}), V_{DD} = 1.8V, V_{REF} = V_{DD}/2 + 1V
		V_{DD} – 25	—	—	mV		V_{DM} = V_{DD}/(2G_{DM}), V_{DD} = 5.5V, V_{REF} = V_{DD}/2 + 1V
Output Short Circuit Current	I_{SC}	—	±8	—	mA		V_{DD} = 1.8V
		—	±30	—	mA		V_{DD} = 5.5V
Power Supply							
Supply Voltage	V_{DD}	1.8	—	5.5	V	all	
Quiescent Current per Amplifier	I_Q	0.5	0.8	1.1	mA		I_O = 0
POR Trip Voltage	V_{PRL}	1.1	1.4	—	V		
	V_{PRH}	—	1.4	1.7	V		

Note 1: V_{CM} = (V_{IP} + V_{IM}) / 2, V_{DM} = (V_{IP} – V_{IM}) and G_{DM} = 1 + R_F/R_G.
2: The V_{OS} spec limits include 1/f noise effects.
3: This is the input offset drift without V_{OS} re-calibration; toggle EN/$\overline{CAL}$ to minimize this effect.
4: These specs apply to both the V_{IP}, V_{IM} input pair (use V_{CM}) and to the V_{REF}, V_{FG} input pair (V_{REF} takes V_{CM}'s place).
5: This spec applies to the V_{IP}, V_{IM}, V_{REF} and V_{FG} pins individually.
6: Figure 2-11 and Figure 2-19 show the V_{IVR} and V_{DMR} variation over temperature.
7: See **Section 1.5 "Explanation of DC Error Specs"**.

TABLE 1-2: AC ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, T_A = 25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

Parameters	Sym	Min	Typ	Max	Units	G_{MIN}	Conditions
AC Response							
Gain Bandwidth Product	GBWP	—	0.50 G_{MIN}	—	MHz	1 to 10	
		—	35	—	MHz	100	
Phase Margin	PM	—	70	—	°	all	
Open-Loop Output Impedance	R_{OL}	—	0.9	—	kΩ	1 to 10	
		—	0.6	—	kΩ	100	
Power Supply Rejection Ratio	PSRR	—	94	—	dB	all	f < 10 kHz
Common Mode Rejection Ratio	CMRR	—	104	—	dB	1 to 10	f < 10 kHz
		—	94	—	dB	100	f < 10 kHz
Step Response							
Slew Rate	SR	—	3	—	V/µs	1 to 10	V_{DD} = 1.8V
		—	9	—	V/µs		V_{DD} = 5.5V
		—	2	—	V/µs	100	V_{DD} = 1.8V
		—	6	—	V/µs		V_{DD} = 5.5V
Overdrive Recovery, Input Common Mode	t_{IRC}	—	10	—	µs	all	V_{CM} = V_{SS} – 1V (or V_{DD} + 1V) to V_{DD}/2, $G_{DM}V_{DM}$ = ±0.1V, 90% of V_{OUT} change
Overdrive Recovery, Input Differential Mode	t_{IRD}	—	5	—	µs		V_{DM} = V_{DML} – (0.5V)/G_{MIN} (or V_{DMH} + (0.5V)/G_{MIN}) to 0V, V_{REF} = (V_{DD} – $G_{DM}V_{DM}$)/2, 90% of V_{OUT} change
Overdrive Recovery, Output	t_{OR}	—	8	—	µs		G_{DM} = 2G_{MIN}, $G_{DM}V_{DM}$ = 0.5V_{DD} to 0V, V_{REF} = 0.75V_{DD} (or 0.25V_{DD}), 90% of V_{OUT} change
Noise							
Input Noise Voltage	E_{ni}	—	570/G_{MIN}	—	μV_{P-P}	1 to 10	f = 0.1 Hz to 10 Hz
		—	18	—	μV_{P-P}	100	
Input Noise Voltage Density	e_{ni}	—	950/G_{MIN}	—	nV/√Hz	1 to 10	f = 100 kHz
		—	35	—	nV/√Hz	100	
Input Current Noise Density	i_{ni}	—	1	—	fA/√Hz	all	f = 1 kHz

TABLE 1-3: DIGITAL ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, T_A = 25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

Parameters	Sym	Min	Typ	Max	Units	G_{MIN}	Conditions
EN/$\overline{CAL}$ Low Specifications							
EN/$\overline{CAL}$ Logic Threshold, Low	V_{IL}	V_{SS}	—	0.2 V_{DD}	V	all	
EN/$\overline{CAL}$ Input Current, Low	I_{ENL}	—	-0.1	—	nA		EN/$\overline{CAL}$ = 0V
GND Current	I_{SS}	-7	-2.5	—	µA		EN/$\overline{CAL}$ = 0V, V_{DD} = 5.5V
Amplifier Output Leakage	$I_{O(LEAK)}$	—	10	—	nA		EN/$\overline{CAL}$ = 0V
EN/$\overline{CAL}$ High Specifications							
EN/$\overline{CAL}$ Logic Threshold, High	V_{IH}	0.8 V_{DD}		V_{DD}	V	all	
EN/$\overline{CAL}$ Input Current, High	I_{ENH}	—	-0.01	—	nA		EN/$\overline{CAL}$ = V_{DD}
EN/$\overline{CAL}$ Dynamic Specifications							
EN/$\overline{CAL}$ Input Hysteresis	V_{HYST}	—	0.2	—	V	all	
EN/$\overline{CAL}$ Low to Amplifier Output High-Z Turn-off Time	t_{OFF}	—	3	10	µs		EN/$\overline{CAL}$ = 0.2V_{DD} to V_{OUT} = 0.1(V_{DD}/2), $V_{DM}G_{DM}$ = 1 V, V_L = 0V
EN/$\overline{CAL}$ High to Amplifier Output On Time	t_{ON}	12	20	28	ms		EN/$\overline{CAL}$ = 0.8V_{DD} to V_{OUT} = 0.9(V_{DD}/2), $V_{DM}G_{DM}$ = 1 V, V_L = 0V
EN/$\overline{CAL}$ Low to EN/$\overline{CAL}$ High low time	t_{ENLH}	100	—	—	µs		Minimum time before externally releasing EN/$\overline{CAL}$ (**Note 1**)
Amplifier On to EN/$\overline{CAL}$ Low Setup Time	t_{ENOL}	—	100	—	µs		
POR Dynamic Specifications							
V_{DD} ↓ to Output Off	t_{PHL}	—	10	—	µs	all	V_L = 0V, V_{DD} = 1.8V to V_{PRL} – 0.1V step, 90% of V_{OUT} change
V_{DD} ↑ to Output On	t_{PLH}	140	250	360	ms		V_L = 0V, V_{DD} = 0V to V_{PRH} + 0.1V step, 90% of V_{OUT} change

Note 1: For design guidance only; not tested.

TABLE 1-4: TEMPERATURE SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, all limits are specified for: V_{DD} = 1.8V to 5.5V, V_{SS} = GND.

Parameters	Sym	Min	Typ	Max	Units	Conditions
Temperature Ranges						
Specified Temperature Range	T_A	-40	—	+125	°C	
Operating Temperature Range	T_A	-40	—	+125	°C	**(Note 1)**
Storage Temperature Range	T_A	-65	—	+150	°C	
Thermal Package Resistances						
Thermal Resistance, 8L-SOIC	θ_{JA}	—	150	—	°C/W	
Thermal Resistance, 8L-TDFN (2×3)	θ_{JA}	—	53	—	°C/W	

Note 1: Operation must not cause T_J to exceed the Absolute Maximum Junction Temperature specification (+150°C).

1.3 Timing Diagrams

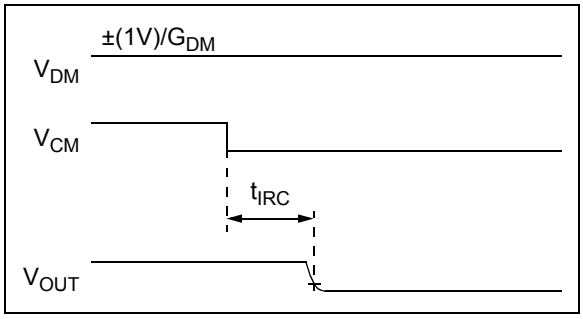


FIGURE 1-1: *Common Mode Input Overdrive Recovery Timing Diagram.*

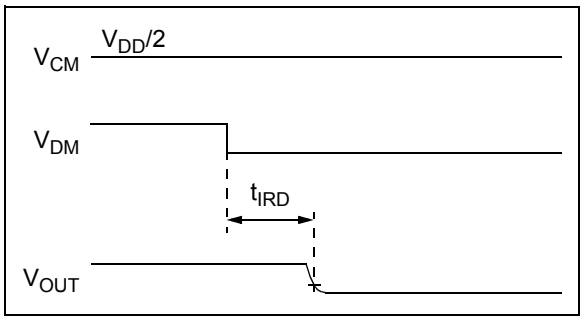


FIGURE 1-2: *Differential Mode Input Overdrive Recovery Timing Diagram.*

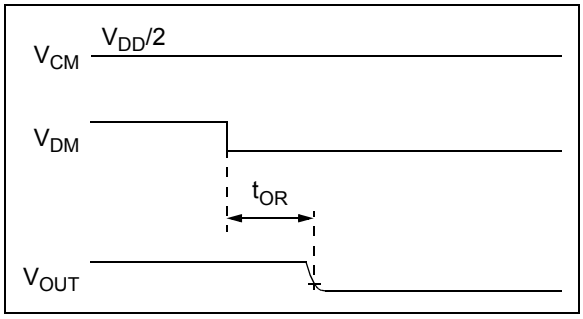


FIGURE 1-3: *Output Overdrive Recovery Timing Diagram.*

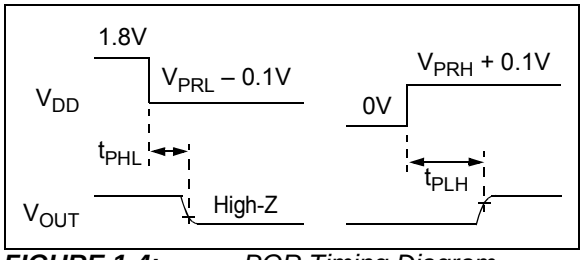


FIGURE 1-4: *POR Timing Diagram.*

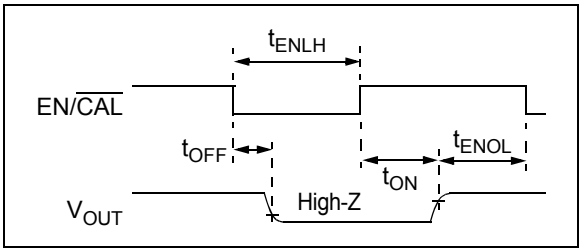


FIGURE 1-5: *EN/$\overline{CAL}$ Timing Diagram.*

1.4 DC Test Circuits

1.4.1 INPUT OFFSET TEST CIRCUIT

Figure 1-6 is used for testing the INA's input offset errors and input voltage range (V_E, V_{IVL} and V_{IVH}; see **Section 1.5.1 "Input Offset Related Errors"** and **Section 1.5.2 "Input Offset Common Mode Non-linearity"**). U_2 is part of a control loop that forces V_{OUT} to equal V_{CNT}; U_1 can be set to any bias point.

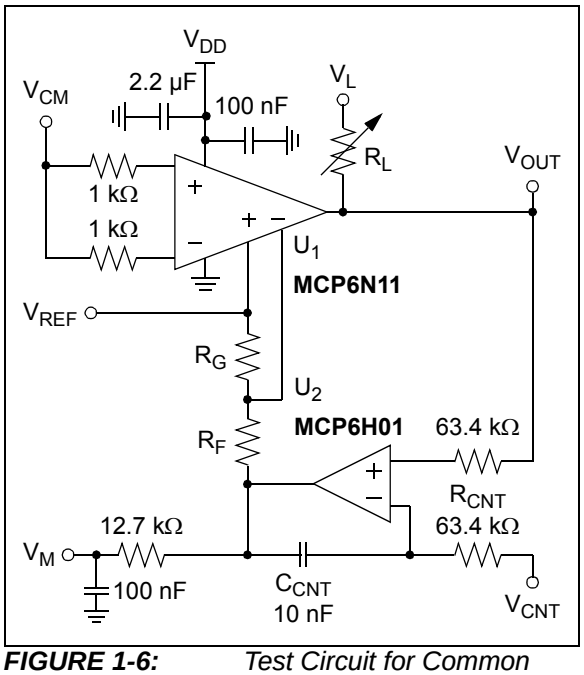


FIGURE 1-6: *Test Circuit for Common Mode (Input Offset).*

When MCP6N11 is in its normal range of operation, the DC output voltages are (where V_E is the sum of input offset errors and g_E is the gain error):

EQUATION 1-1:

$$\begin{aligned} G_{DM} &= 1 + R_F/R_G \\ V_{OUT} &= V_{CNT} \\ V_M &= V_{REF} + G_{DM}(1 + g_E)V_E \end{aligned}$$

Table 1-5 gives the recommended R_F and R_G values for different G_{MIN} options.

TABLE 1-5: SELECTING R_F AND R_G

G_{MIN} (V/V) Nom.	R_F (Ω) Nom.	R_G (Ω) Nom.	G_{DM} (V/V) Nom.	$G_{DM}V_{OS}$ (±V) Max.	BW (kHz) Nom.
1	100k	499	201.4	0.60	2.5
2				0.40	5.0
5	100k	100	1001	0.85	2.5
10				0.50	5.0
100				0.35	35

1.4.2 DIFFERENTIAL GAIN TEST CIRCUIT

Figure 1-7 is used for testing the INA's differential gain error, non-linearity and input voltage range (g_E, INL_{DM}, V_{DML} and V_{DMH}; see **Section 1.5.3 "Differential Gain Error and Non-linearity"**). R_F and R_G are 0.01% for accurate gain error measurements.

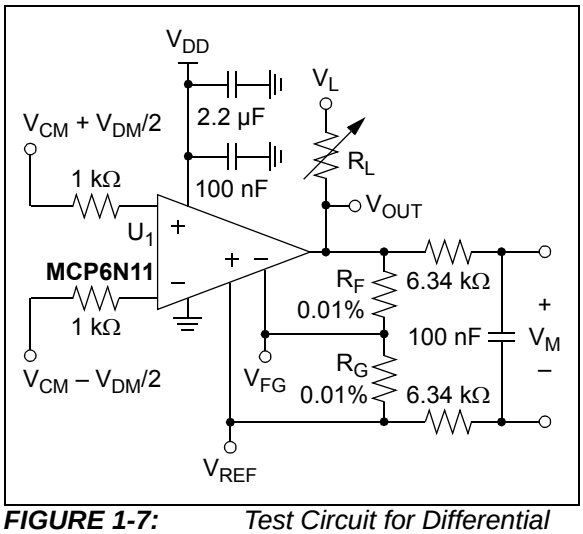


FIGURE 1-7: *Test Circuit for Differential Mode.*

The output voltages are (where V_E is the sum of input offset errors and g_E is the gain error):

EQUATION 1-2:

$$\begin{aligned} G_{DM} &= 1 + R_F/R_G \\ V_{OUT} &= V_{REF} + G_{DM}(1 + g_E)(V_{DM} + V_E) \\ V_M &= V_{OUT} - V_{REF} \\ &= G_{DM}(1 + g_E)(V_{DM} + V_E) \end{aligned}$$

To keep V_{REF}, V_{FG} and V_{OUT} within their ranges, set:

EQUATION 1-3:

$$V_{REF} = (V_{DD} - G_{DM}V_{DM})/2$$

Table 1-6 shows the recommended R_F and R_G. They produce a 10 kΩ load; V_L can usually be left open.

TABLE 1-6: SELECTING R_F AND R_G

G_{MIN} (V/V) Nom.	R_F (Ω) Nom.	R_G (Ω) Nom.	G_{DM} (V/V) Nom.
1	0	Open	1.000
2	4.99k	4.99k	2.000
5	8.06k	2.00k	5.030
10	9.09k	1.00k	10.09
100	10.0k	100	101.0

1.5 Explanation of DC Error Specs

1.5.1 INPUT OFFSET RELATED ERRORS

The input offset error (V_E) is extracted from input offset measurements (see **Section 1.4.1 "Input Offset Test Circuit"**), based on Equation 1-1:

EQUATION 1-4:

$$V_E = \frac{V_M - V_{REF}}{G_{DM}(1 + g_E)}$$

V_E has several terms, which assume a linear response to changes in V_{DD}, V_{SS}, V_{CM}, V_{OUT} and T_A (all of which are in their specified ranges):

EQUATION 1-5:

$$V_E = V_{OS} + \frac{\Delta V_{DD} - \Delta V_{SS}}{PSRR} + \frac{\Delta V_{CM}}{CMRR} + \frac{\Delta V_{REF}}{CMRR} + \frac{\Delta V_{OUT}}{A_{OL}} + \Delta T_A \cdot \frac{\Delta V_{OS}}{\Delta T_A}$$

Where:

PSRR, *CMRR* and A_{OL} are in units of V/V

ΔT_A is in units of °C

V_{DM} = 0

Equation 1-2 shows how V_E affects V_{OUT}.

1.5.2 INPUT OFFSET COMMON MODE NON-LINEARITY

The input offset error (V_E) changes non-linearly with V_{CM}. Figure 1-8 shows V_E vs. V_{CM}, as well as a linear fit line (V_{E_LIN}) based on V_{OS} and CMRR. The op amp is in standard conditions (ΔV_{OUT} = 0, V_{DM} = 0, etc.). V_{CM} is swept from V_{IVL} to V_{IVH}. The test circuit is in **Section 1.4.1 "Input Offset Test Circuit"** and V_E is calculated using Equation 1-4.

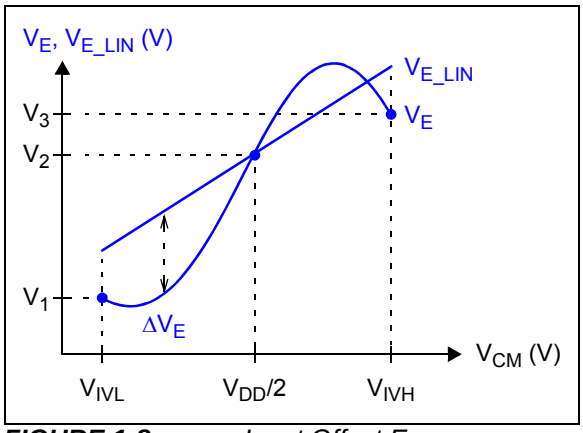


FIGURE 1-8: *Input Offset Error vs. Common Mode Input Voltage.*

Based on the measured V_E data, we obtain the following linear fit:

EQUATION 1-6:

$$V_{E\_LIN} = V_{OS} + \frac{V_{CM} - V_{DD}/2}{CMRR}$$

Where:

$$V_{OS} = V_2$$

$$\frac{1}{CMRR} = \frac{V_3 - V_1}{V_{IVH} - V_{IVL}}$$

The remaining error (ΔV_E) is described by the Common Mode Non-Linearity spec:

EQUATION 1-7:

$$INL_{CM} = \frac{max|\Delta V_E|}{V_{IVH} - V_{IVL}}$$

Where:

$$\Delta V_E = V_E - V_{E\_LIN}$$

The same common mode behavior applies to V_E when V_{REF} is swept, instead of V_{CM}, since both input stages are designed the same:

EQUATION 1-8:

$$V_{E\_LIN} = V_{OS} + \frac{V_{REF} - V_{DD}/2}{CMRR}$$

$$INL_{CM} = \frac{max|\Delta V_E|}{V_{IVH} - V_{IVL}}$$

1.5.3 DIFFERENTIAL GAIN ERROR AND NON-LINEARITY

The differential errors are extracted from differential gain measurements (see **Section 1.4.2 "Differential Gain Test Circuit"**), based on Equation 1-2. These errors are the differential gain error (g_E) and the input offset error (V_E, which changes non-linearly with V_{DM}):

EQUATION 1-9:

$$G_{DM} = 1 + R_F/R_G$$

$$V_M = G_{DM}(1 + g_E)(V_{DM} + V_E)$$

These errors are adjusted for the expected output, then referred back to the input, giving the differential input error (V_{ED}) as a function of V_{DM}:

EQUATION 1-10:

$$V_{ED} = \frac{V_M}{G_{DM}} - V_{DM}$$

Figure 1-9 shows V_{ED} vs. V_{DM}, as well as a linear fit line (V_{ED_LIN}) based on V_E and g_E. The op amp is in standard conditions (ΔV_{OUT} = 0, etc.). V_{DM} is swept from V_{DML} to V_{DMH}.

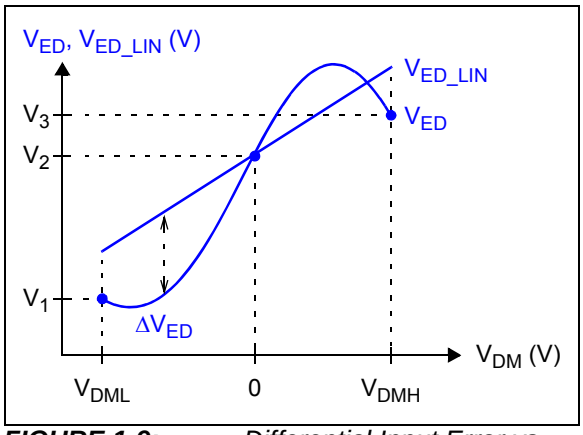


FIGURE 1-9: *Differential Input Error vs. Differential Input Voltage.*

Based on the measured V_{ED} data, we obtain the following linear fit:

EQUATION 1-11:

$$V_{ED\_LIN} = (1 + g_E)V_E + g_E V_{DM}$$

Where:

$$g_E = \frac{V_3 - V_1}{V_{DMH} - V_{DML}} - 1$$

$$V_E = \frac{V_2}{1 + g_E}$$

Note that the V_E value measured here is not as accurate as the one obtained in **Section 1.5.1 "Input Offset Related Errors"**.

The remaining error (ΔV_{ED}) is described by the Differential Mode Non-Linearity spec:

EQUATION 1-12:

$$INL_{DM} = \frac{max|\Delta V_{ED}|}{V_{DMH} - V_{DML}}$$

Where:

$$\Delta V_{ED} = V_{ED} - V_{ED\_LIN}$$

NOTES:

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

2.1 DC Voltages and Currents

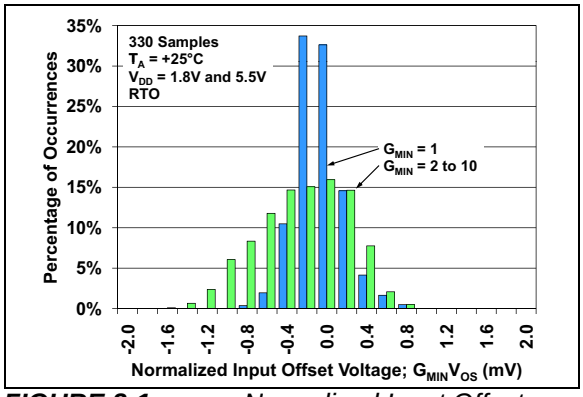


FIGURE 2-1: *Normalized Input Offset Voltage, with G_{MIN} = 1 to 10.*

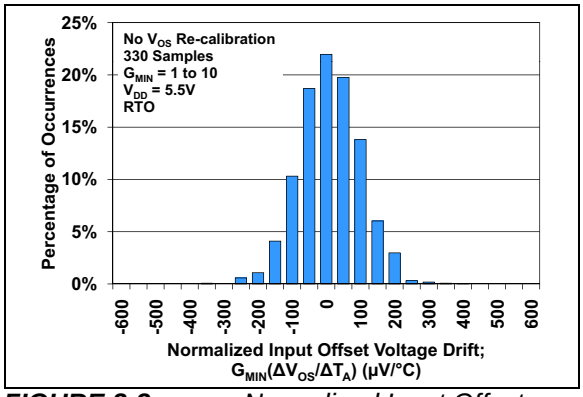


FIGURE 2-3: *Normalized Input Offset Voltage Drift, with G_{MIN} = 1 to 10.*

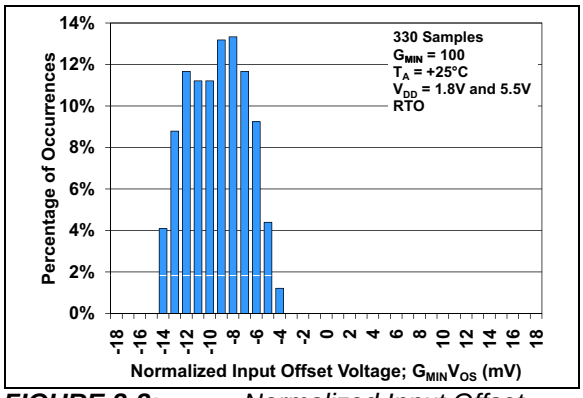


FIGURE 2-2: *Normalized Input Offset Voltage, with G_{MIN} = 100.*

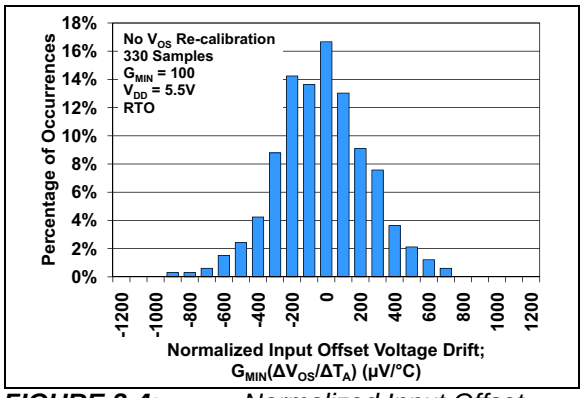


FIGURE 2-4: *Normalized Input Offset Voltage Drift, with G_{MIN} = 100.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = $V_{DD}/2$, V_{DM} = 0V, V_{REF} = $V_{DD}/2$, V_L = $V_{DD}/2$, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

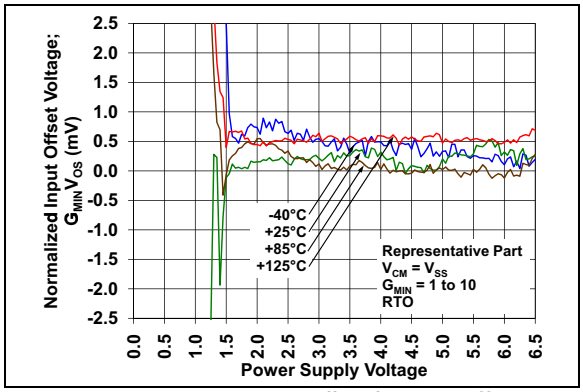


FIGURE 2-5: *Normalized Input Offset Voltage vs. Power Supply Voltage, with V_{CM} = 0V and G_{MIN} = 1 to 10.*

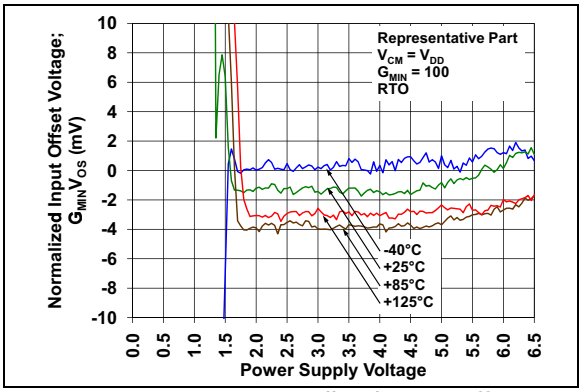


FIGURE 2-8: *Normalized Input Offset Voltage vs. Power Supply Voltage, with V_{CM} = V_{DD} and G_{MIN} = 100.*

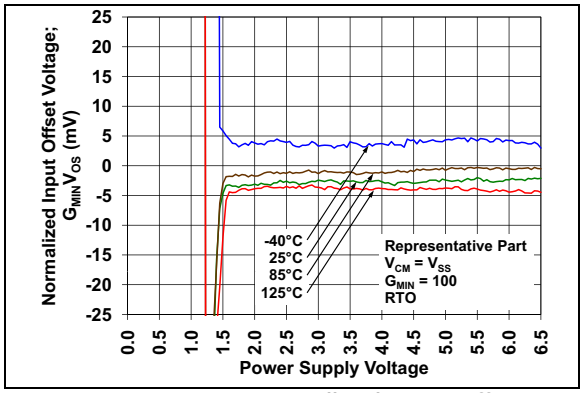


FIGURE 2-6: *Normalized Input Offset Voltage vs. Power Supply Voltage, with V_{CM} = 0V and G_{MIN} = 100.*

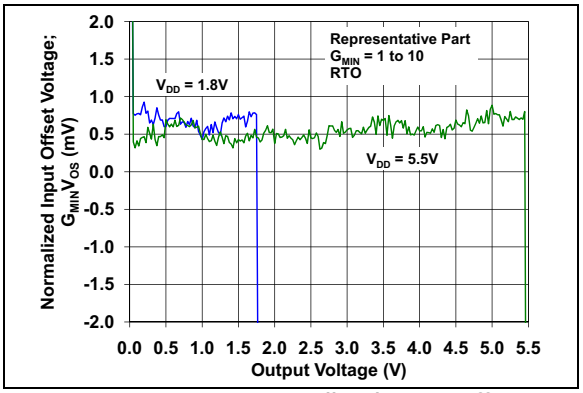


FIGURE 2-9: *Normalized Input Offset Voltage vs. Output Voltage, with G_{MIN} = 1 to 10.*

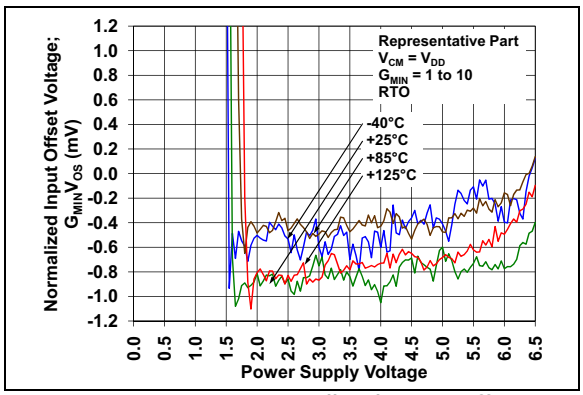


FIGURE 2-7: *Normalized Input Offset Voltage vs. Power Supply Voltage, with V_{CM} = V_{DD} and G_{MIN} = 1 to 10.*

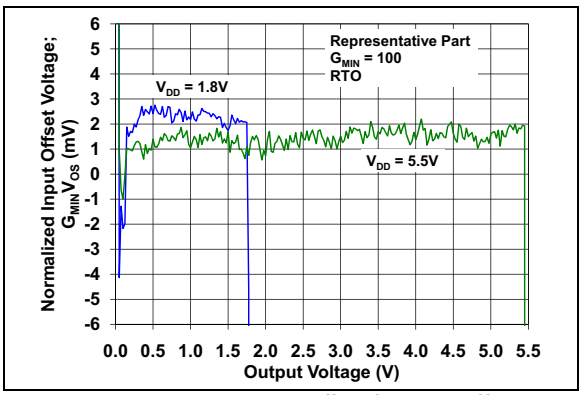


FIGURE 2-10: *Normalized Input Offset Voltage vs. Output Voltage, with G_{MIN} = 100.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

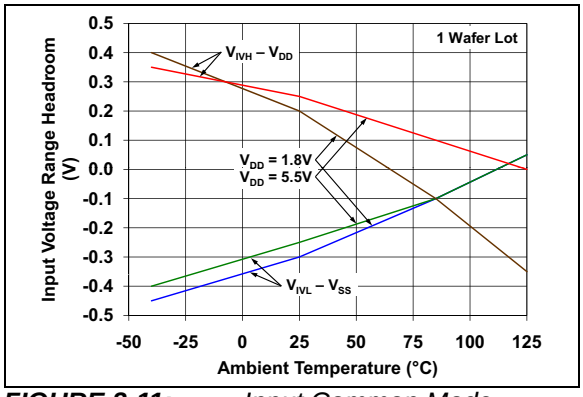


FIGURE 2-11: *Input Common Mode Voltage Headroom vs. Ambient Temperature.*

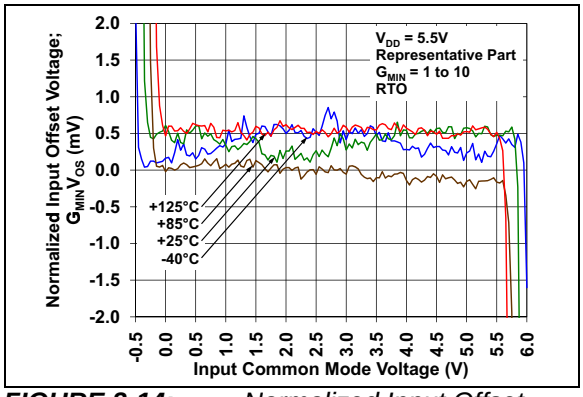


FIGURE 2-14: *Normalized Input Offset Voltage vs. Common Mode Voltage, with V_{DD} = 5.5V and G_{MIN} = 1 to 10.*

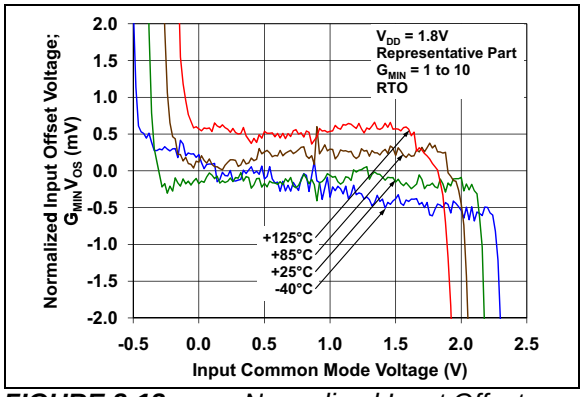


FIGURE 2-12: *Normalized Input Offset Voltage vs. Common Mode Voltage, with V_{DD} = 1.8V and G_{MIN} = 1 to 10.*

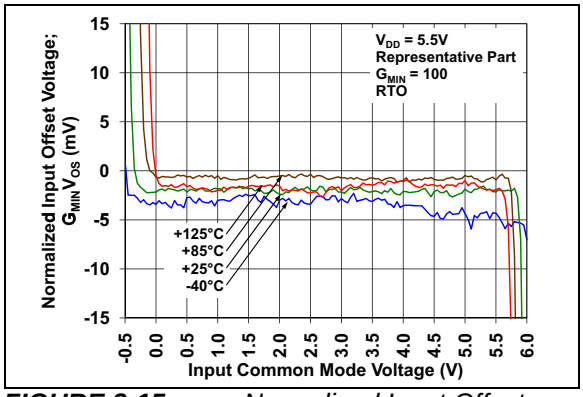


FIGURE 2-15: *Normalized Input Offset Voltage vs. Common Mode Voltage, with V_{DD} = 5.5V and G_{MIN} = 100.*

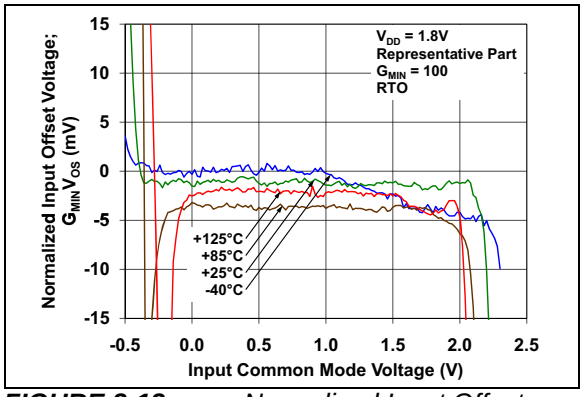


FIGURE 2-13: *Normalized Input Offset Voltage vs. Common Mode Voltage, with V_{DD} = 1.8V and G_{MIN} = 100.*

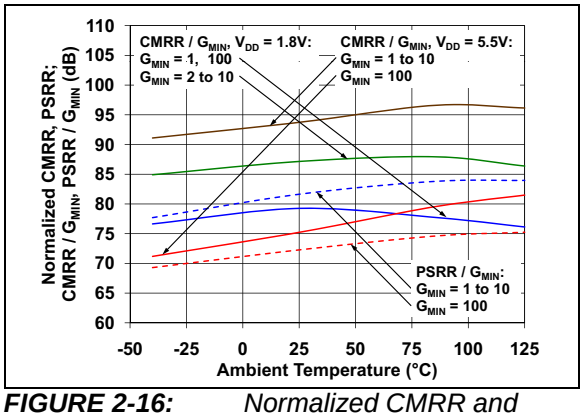


FIGURE 2-16: *Normalized CMRR and PSRR vs. Ambient Temperature.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

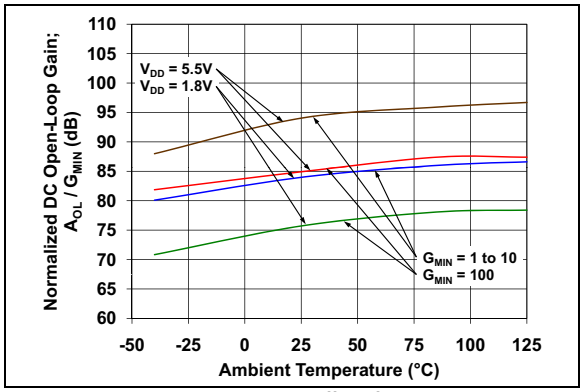


FIGURE 2-17: *Normalized DC Open-Loop Gain vs. Ambient Temperature.*

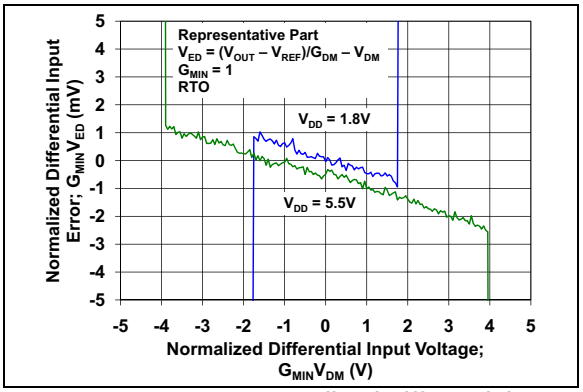


FIGURE 2-20: *Normalized Differential Input Error vs. Differential Voltage, with G_{MIN} = 1.*

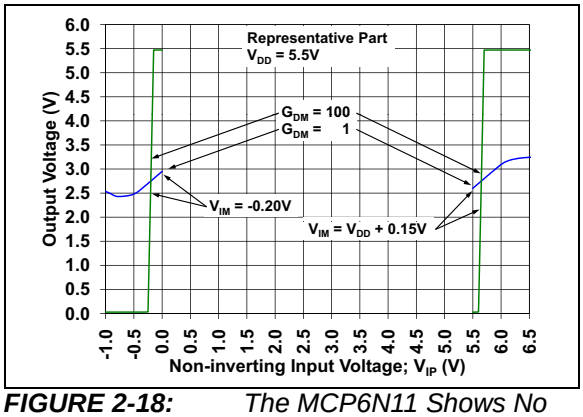


FIGURE 2-18: *The MCP6N11 Shows No Phase Reversal vs. Common Mode Voltage.*

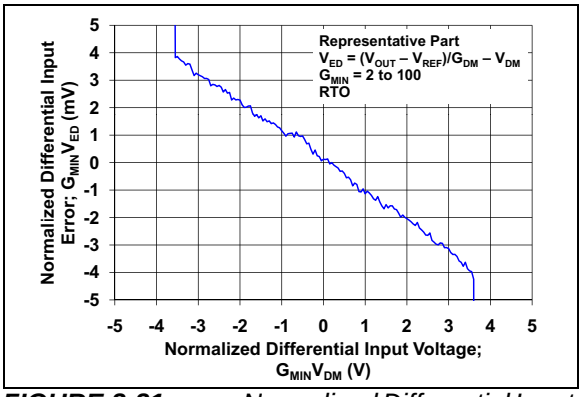


FIGURE 2-21: *Normalized Differential Input Error vs. Differential Voltage, with G_{MIN} = 2 to 100.*

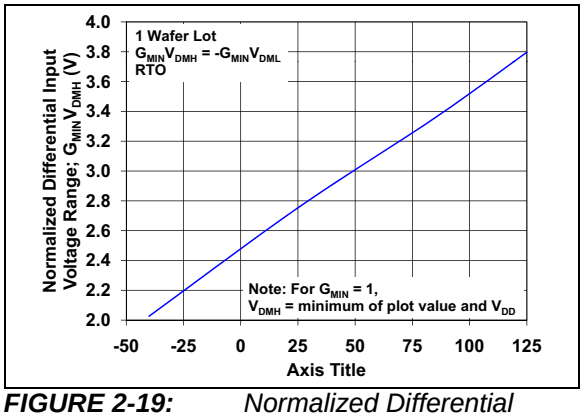


FIGURE 2-19: *Normalized Differential Mode Voltage Range vs. Ambient Temperature.*

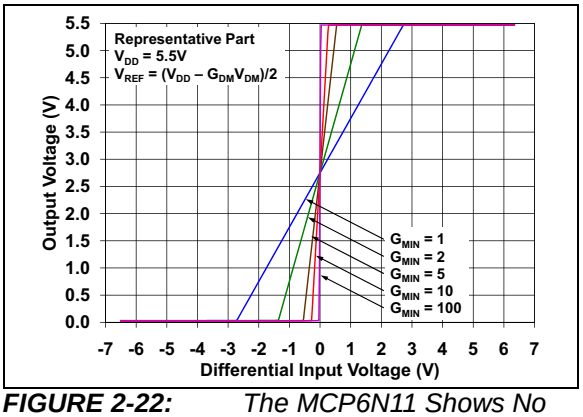


FIGURE 2-22: *The MCP6N11 Shows No Phase Reversal vs. Differential Voltage, with V_{DD} = 5.5V.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

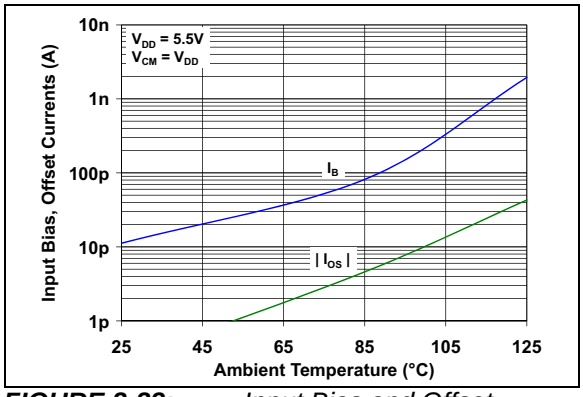


FIGURE 2-23: *Input Bias and Offset Currents vs. Ambient Temperature, with V_{DD} = +5.5V.*

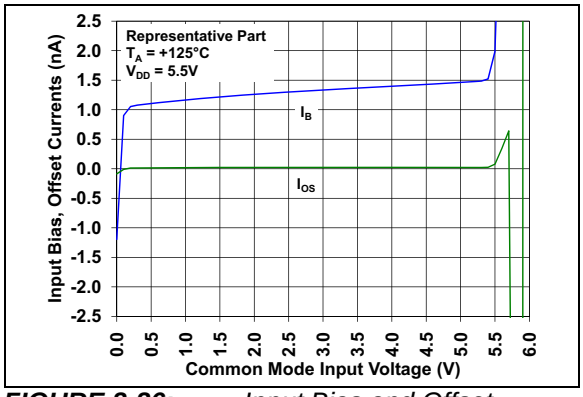


FIGURE 2-26: *Input Bias and Offset Currents vs. Common Mode Input Voltage, with T_A = +125°C.*

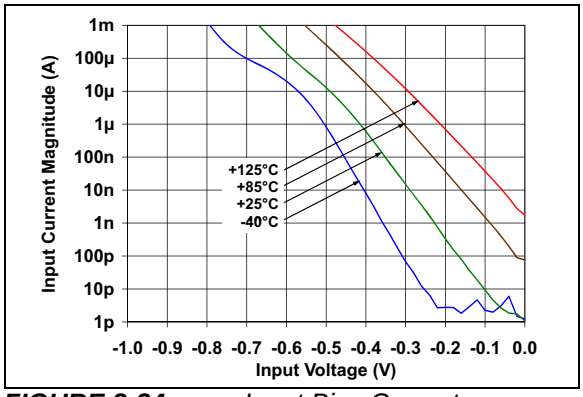


FIGURE 2-24: *Input Bias Current vs. Input Voltage (below V_{SS}).*

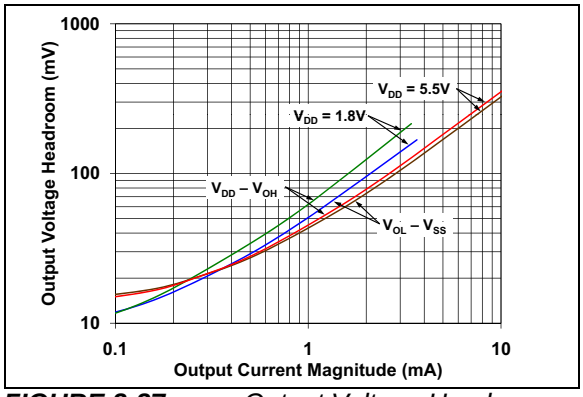


FIGURE 2-27: *Output Voltage Headroom vs. Output Current.*

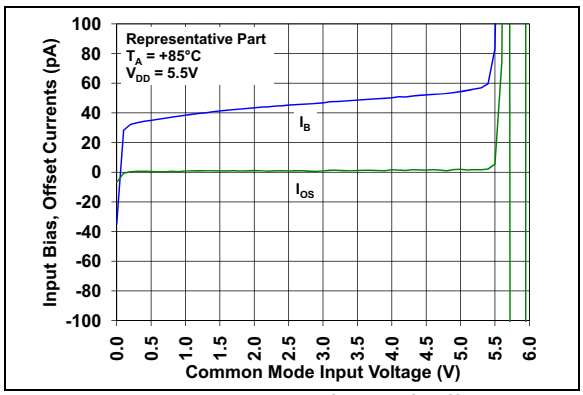


FIGURE 2-25: *Input Bias and Offset Currents vs. Common Mode Input Voltage, with T_A = +85°C.*

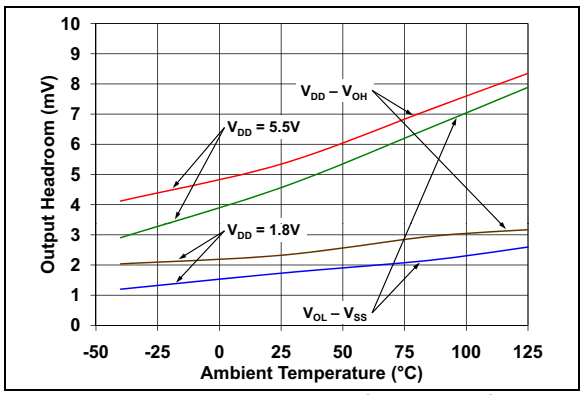


FIGURE 2-28: *Output Voltage Headroom vs. Ambient Temperature.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

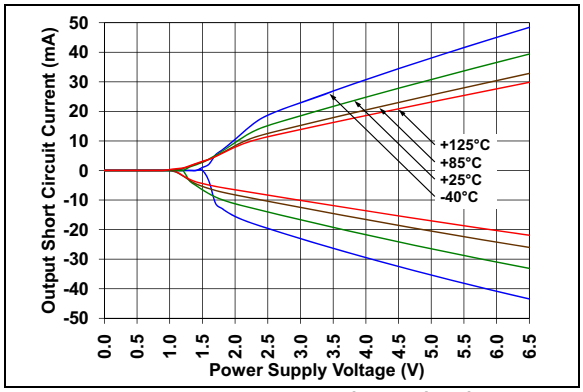


FIGURE 2-29: *Output Short Circuit Current vs. Power Supply Voltage.*

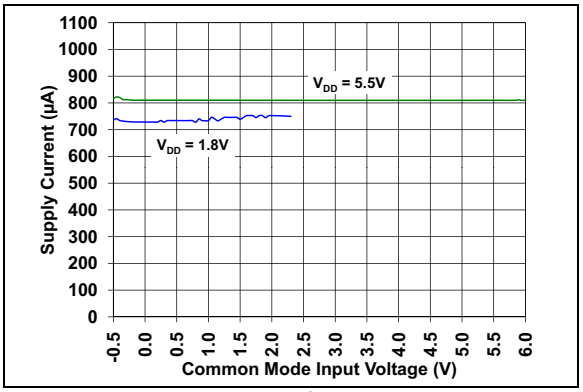


FIGURE 2-31: *Supply Current vs. Common Mode Input Voltage.*

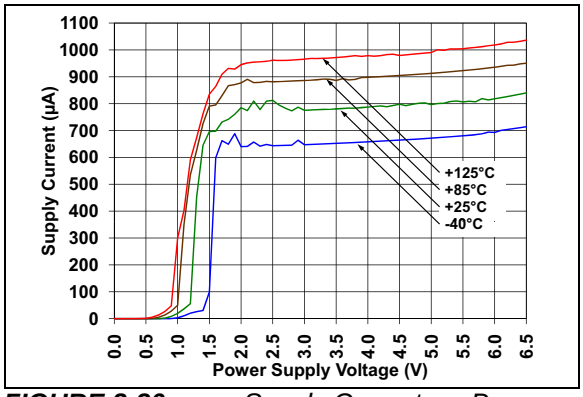


FIGURE 2-30: *Supply Current vs. Power Supply Voltage.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

2.2 Frequency Response

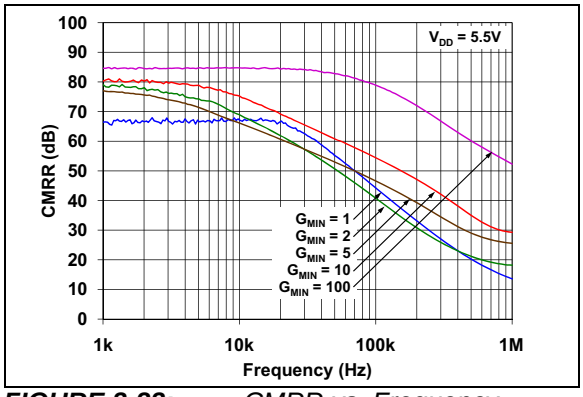


FIGURE 2-32: *CMRR vs. Frequency.*

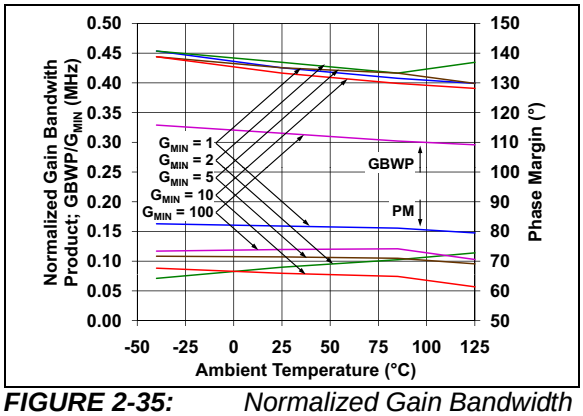


FIGURE 2-35: *Normalized Gain Bandwidth Product and Phase Margin vs. Ambient Temperature.*

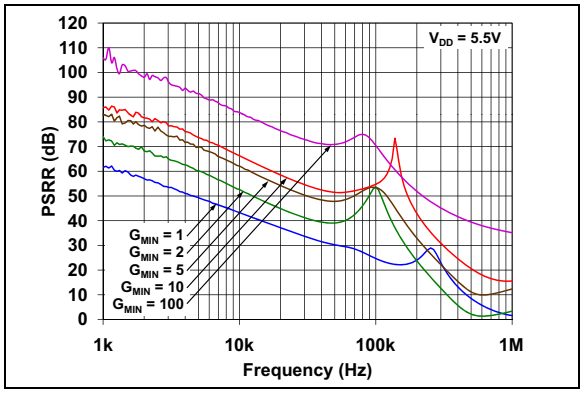


FIGURE 2-33: *PSRR vs. Frequency.*

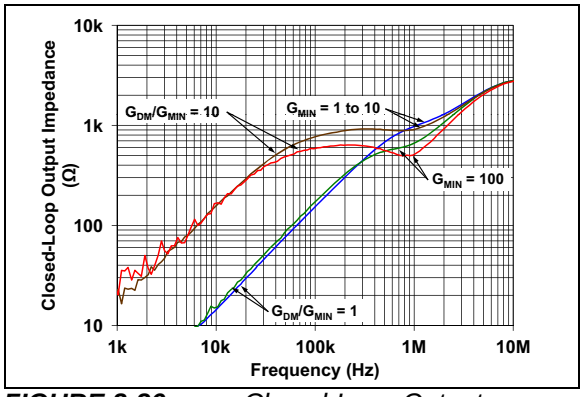


FIGURE 2-36: *Closed-Loop Output Impedance vs. Frequency.*

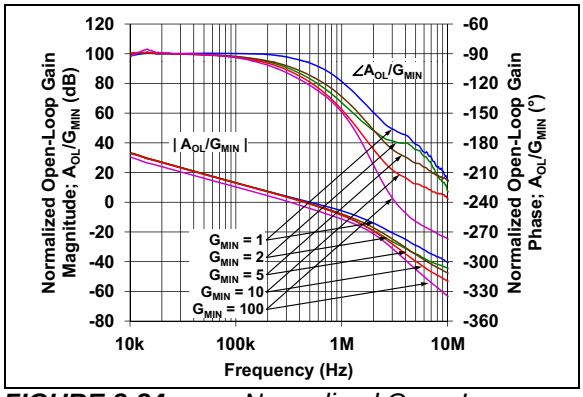


FIGURE 2-34: *Normalized Open-Loop Gain vs. Frequency.*

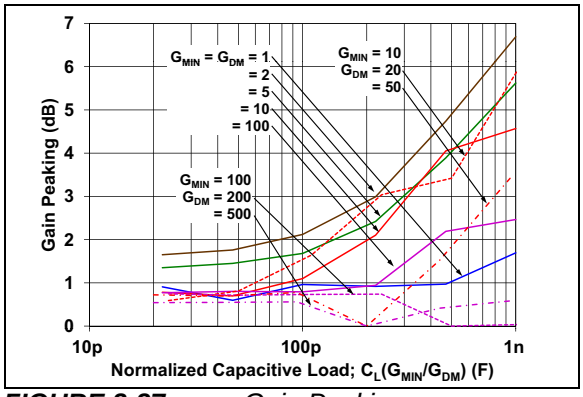


FIGURE 2-37: *Gain Peaking vs. Normalized Capacitive Load.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = $V_{DD}/2$, V_{DM} = 0V, V_{REF} = $V_{DD}/2$, V_L = $V_{DD}/2$, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

2.3 Noise

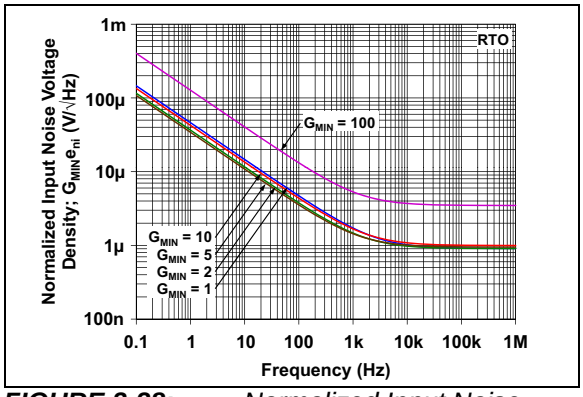


FIGURE 2-38: *Normalized Input Noise Voltage Density vs. Frequency.*

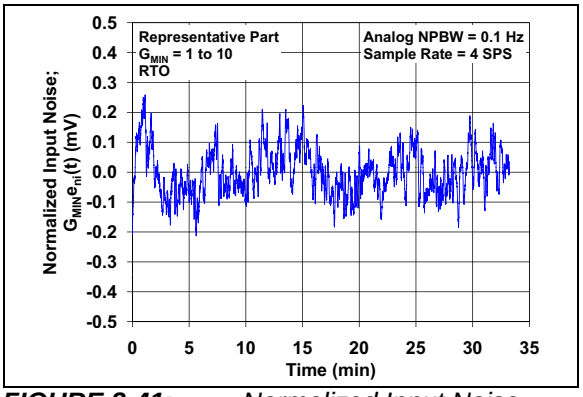


FIGURE 2-41: *Normalized Input Noise Voltage vs. Time, with G_{MIN} = 1 to 10.*

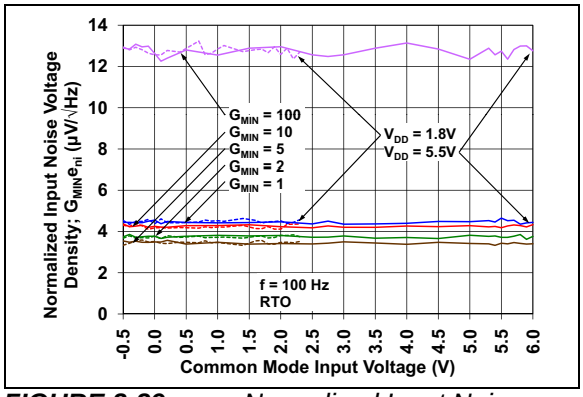


FIGURE 2-39: *Normalized Input Noise Voltage Density vs. Input Common Mode Voltage, with f = 100 Hz.*

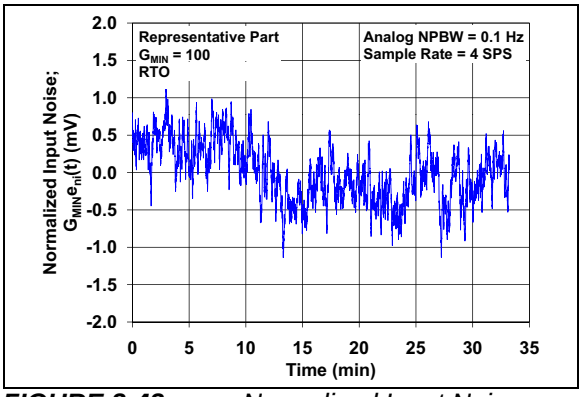


FIGURE 2-42: *Normalized Input Noise Voltage vs. Time, with G_{MIN} = 100.*

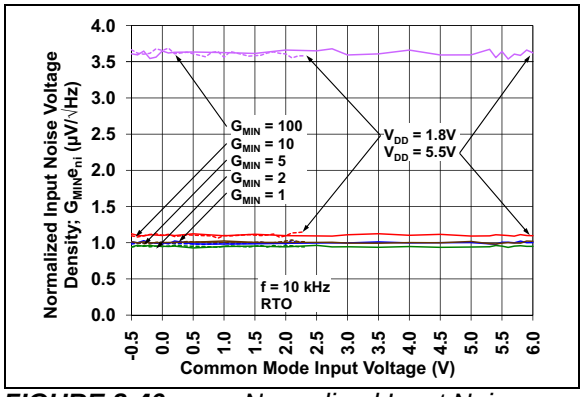


FIGURE 2-40: *Normalized Input Noise Voltage Density vs. Input Common Mode Voltage, with f = 10 kHz.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

2.4 Time Response

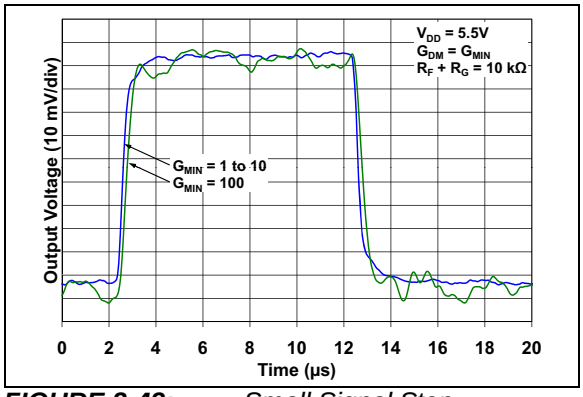


FIGURE 2-43: *Small Signal Step Response.*

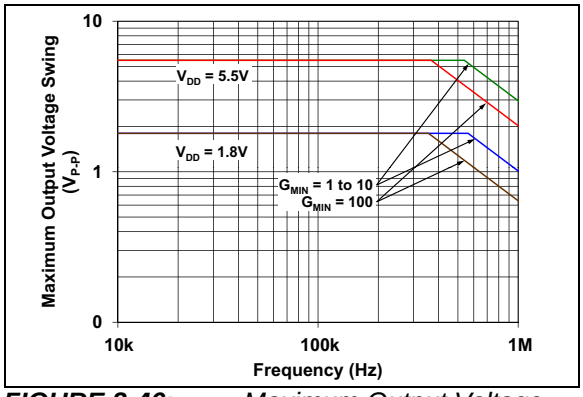


FIGURE 2-46: *Maximum Output Voltage Swing vs. Frequency.*

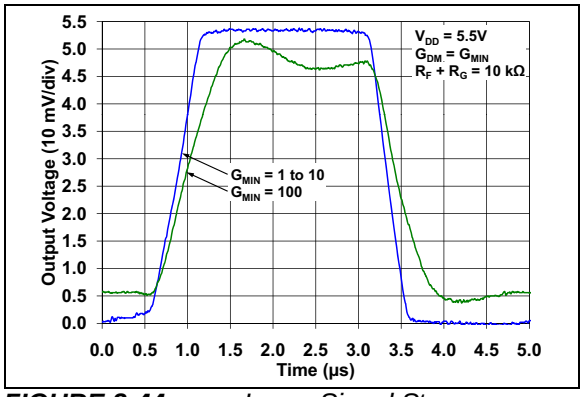


FIGURE 2-44: *Large Signal Step Response.*

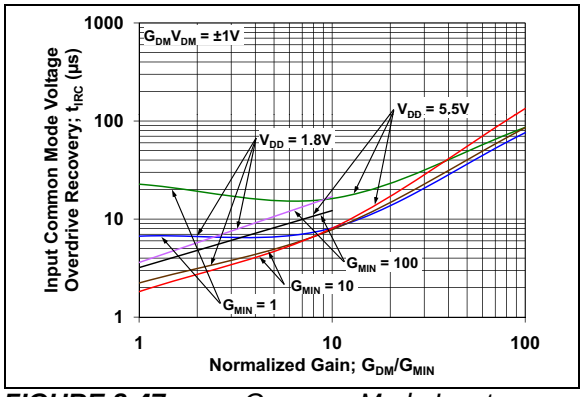


FIGURE 2-47: *Common Mode Input Overdrive Recovery Time vs. Normalized Gain.*

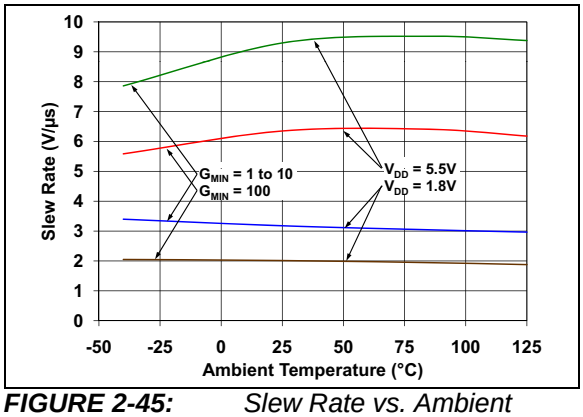


FIGURE 2-45: *Slew Rate vs. Ambient Temperature.*

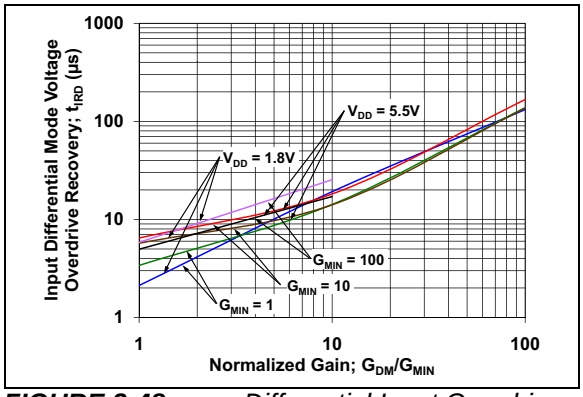


FIGURE 2-48: *Differential Input Overdrive Recovery Time vs. Normalized Gain.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

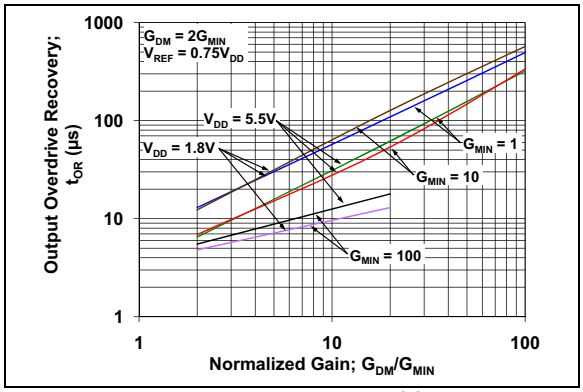


FIGURE 2-49: *Output Overdrive Recovery Time vs. Normalized Gain.*

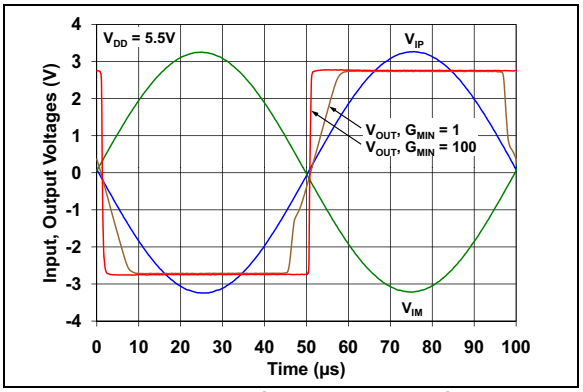


FIGURE 2-51: *The MCP6N11 Shows No Phase Reversal vs. Differential Input Overdrive, with V_{DD} = 5.5V.*

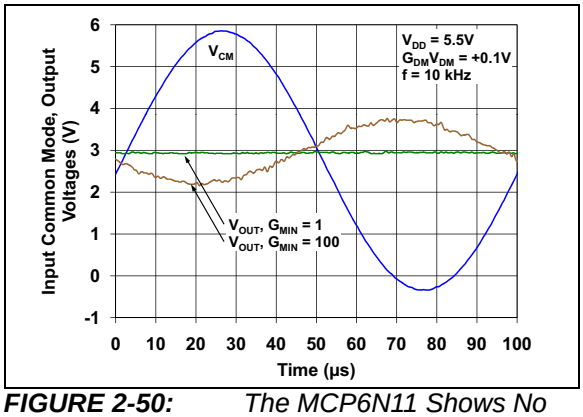


FIGURE 2-50: *The MCP6N11 Shows No Phase Reversal vs. Common Mode Input Overdrive, with V_{DD} = 5.5V.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

2.5 Enable/Calibration and POR Responses

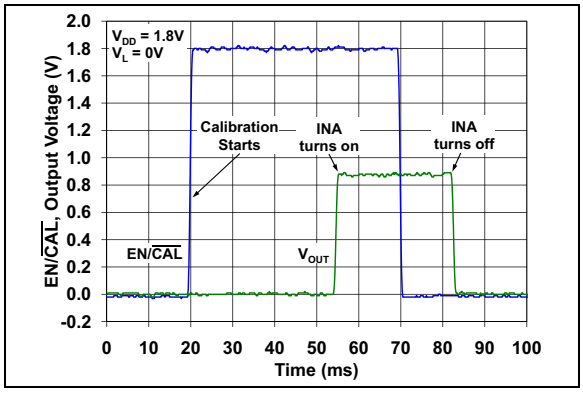


FIGURE 2-52: *EN/$\overline{CAL}$ and Output Voltage vs. Time, with V_{DD} = 1.8V.*

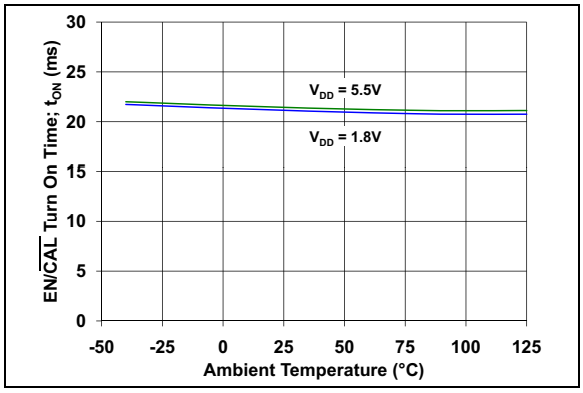


FIGURE 2-55: *EN/$\overline{CAL}$ Turn On Time vs. Ambient Temperature.*

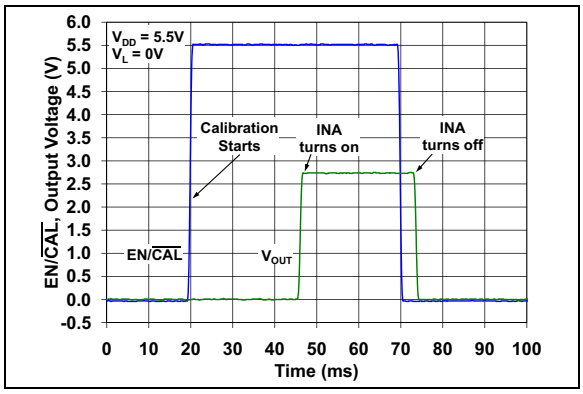


FIGURE 2-53: *EN/$\overline{CAL}$ and Output Voltage vs. Time, with V_{DD} = 5.5V*

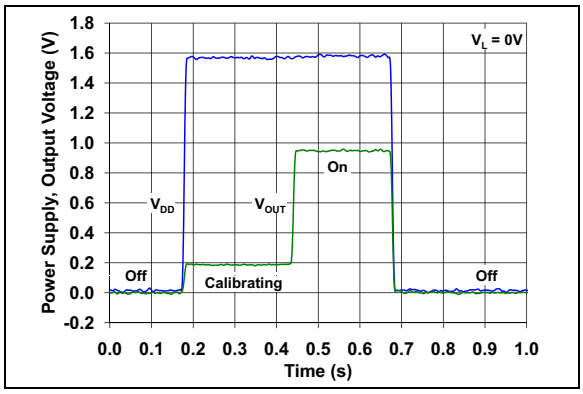


FIGURE 2-56: *Power Supply On and Off and Output Voltage vs. Time.*

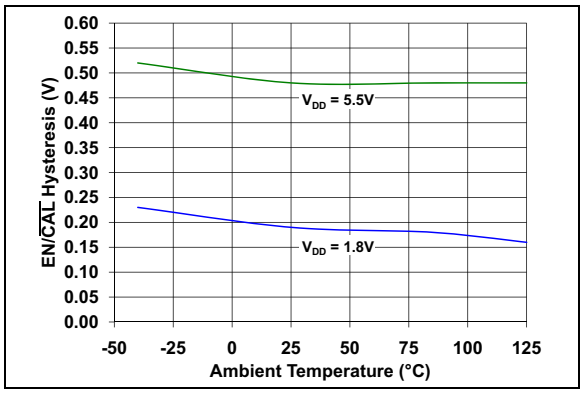


FIGURE 2-54: *EN/$\overline{CAL}$ Hysteresis vs. Ambient Temperature.*

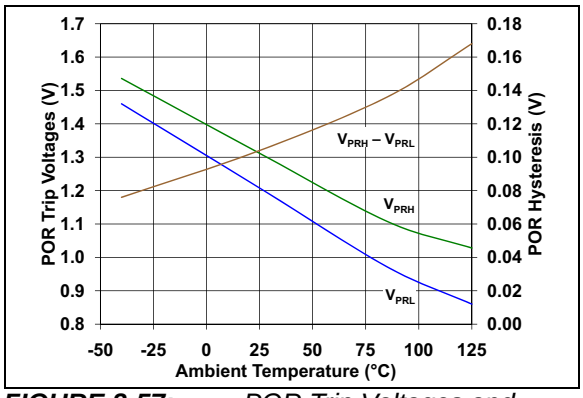


FIGURE 2-57: *POR Trip Voltages and Hysteresis vs. Temperature.*

Note: Unless otherwise indicated, T_A = +25°C, V_{DD} = 1.8V to 5.5V, V_{SS} = GND, EN/$\overline{CAL}$ = V_{DD}, V_{CM} = V_{DD}/2, V_{DM} = 0V, V_{REF} = V_{DD}/2, V_L = V_{DD}/2, R_L = 10 kΩ to V_L, C_L = 60 pF and G_{DM} = G_{MIN}; see Figure 1-6 and Figure 1-7.

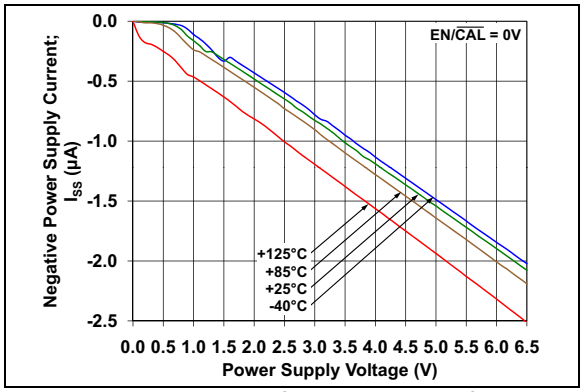


FIGURE 2-58: *Quiescent Current in Shutdown vs. Power Supply Voltage.*

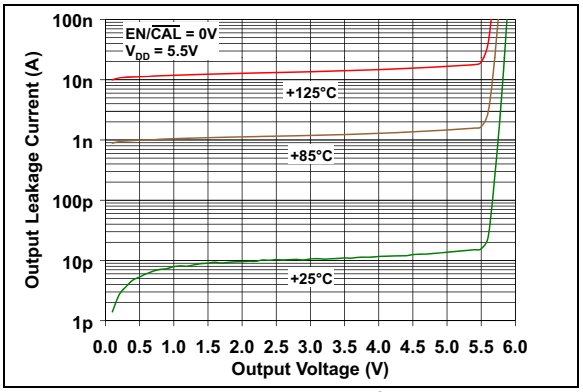


FIGURE 2-59: *Output Leakage Current vs. Output Voltage.*

3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

MCP6N11		Symbol	Description
SOIC	TDFN		
1	1	V_{FG}	Feedback Input
2	2	V_{IM}	Inverting Input
3	3	V_{IP}	Non-inverting Input
4	4	V_{SS}	Negative Power Supply
5	5	V_{REF}	Reference Input
6	6	V_{OUT}	Output
7	7	V_{DD}	Positive Power Supply
8	8	EN/$\overline{CAL}$	Enable/V_{OS} Calibrate Digital Input
—	9	EP	Exposed Thermal Pad (EP); must be connected to V_{SS}

3.1 Analog Signal Inputs

The non-inverting and inverting inputs (V_{IP}, and V_{IM}) are high-impedance CMOS inputs with low bias currents.

3.2 Analog Feedback Input

The analog feedback input (V_{FG}) is the inverting input of the second input stage. The external feedback components (R_F and R_G) are connected to this pin. It is a high-impedance CMOS input with low bias current.

3.3 Analog Reference Input

The analog reference input (V_{REF}) is the non-inverting input of the second input stage; it shifts V_{OUT} to its desired range. The external gain resistor (R_G) is connected to this pin. It is a high-impedance CMOS input with low bias current.

3.4 Analog Output

The analog output (V_{OUT}) is a low-impedance voltage output. It represents the differential input voltage ($V_{DM} = V_{IP} – V_{IM}$), with gain G_{DM} and is shifted by V_{REF}. The external feedback resistor (R_F) is connected to this pin.

3.5 Power Supply Pins

The positive power supply (V_{DD}) is 1.8V to 5.5V higher than the negative power supply (V_{SS}). For normal operation, the other pins are between V_{SS} and V_{DD}.

Typically, these parts are used in a single (positive) supply configuration. In this case, V_{SS} is connected to ground and V_{DD} is connected to the supply; V_{DD} will need bypass capacitors.

3.6 Digital Enable and V_{OS} Calibration Input

This input (EN/$\overline{CAL}$) is a CMOS, Schmitt-triggered input that controls the active, low power and V_{OS} calibration modes of operation. When this pin goes low, the part is placed into a low power mode and the output is high-Z. When this pin goes high, the amplifier's input offset voltage is corrected by the calibration circuitry, then the output is re-connected to the V_{OUT} pin, which becomes low impedance, and the part resumes normal operation.

3.7 Exposed Thermal Pad (EP)

There is an internal connection between the Exposed Thermal Pad (EP) and the V_{SS} pin; they must be connected to the same potential on the Printed Circuit Board (PCB).

This pad can be connected to a PCB ground plane to provide a larger heat sink. This improves the package thermal resistance (θ_{JA}).

NOTES:

4.0 APPLICATIONS

The MCP6N11 instrumentation amplifier (INA) is manufactured using Microchip's state of the art CMOS process. It is low cost, low power and high speed, making it ideal for battery-powered applications.

4.1 Basic Performance

4.1.1 STANDARD CIRCUIT

Figure 4-1 shows the standard circuit configuration for these INAs. When the inputs and output are in their specified ranges, the output voltage is approximately:

EQUATION 4-1:

$$V_{OUT} \approx V_{REF} + G_{DM}V_{DM}$$

Where:

$$G_{DM} = 1 + R_F / R_G$$

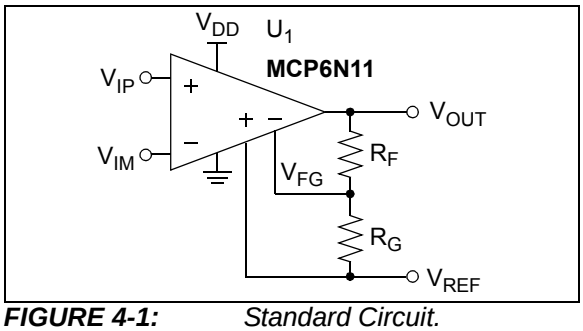


FIGURE 4-1: *Standard Circuit.*

For normal operation, keep:

- V_{IP}, V_{IM}, V_{REF} and V_{FG} between V_{IVL} and V_{IVH}
- $V_{IP} – V_{IM}$ (i.e., V_{DM}) between V_{DML} and V_{DMH}
- V_{OUT} between V_{OL} and V_{OH}

4.1.2 ARCHITECTURE

Figure 4-2 shows the block diagram for these INAs.

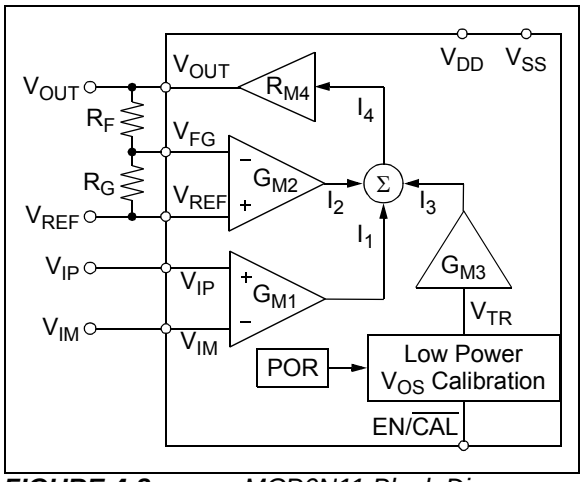


FIGURE 4-2: *MCP6N11 Block Diagram.*

The input offset voltage (V_{OS}) is corrected by the voltage V_{TR}. Each time a V_{OS} Calibration event occurs, V_{TR} is updated to the best value (at that moment). These events are triggered by either powering up (monitored by the POR) or by toggling the EN/$\overline{CAL}$ pin high. The current out of G_{M3} (I_3) is constant and very small (assumed to be zero in the following discussion).

The input signal is applied to G_{M1}. Equation 4-2 shows the relationships between the input voltages (V_{IP} and V_{IM}) and the common mode and differential voltages (V_{CM} and V_{DM}).

EQUATION 4-2:

$$\begin{aligned} V_{IP} &= V_{CM} + V_{DM}/2 \\ V_{IM} &= V_{CM} - V_{DM}/2 \\ V_{CM} &= (V_{IP} + V_{IM})/2 \\ V_{DM} &= V_{IP} - V_{IM} \end{aligned}$$

The negative feedback loop includes G_{M2}, R_{M4}, R_F and R_G. These blocks set the DC open-loop gain (A_{OL}) and the nominal differential gain (G_{DM}):

EQUATION 4-3:

$$\begin{aligned} A_{OL} &= G_{M2}R_{M4} \\ G_{DM} &= 1 + R_F/R_G \end{aligned}$$

A_{OL} is very high, so I_4 is very small and $I_1 + I_2 \approx 0$. This makes the differential inputs to G_{M1} and G_{M2} equal in magnitude and opposite in polarity. Ideally, this gives:

EQUATION 4-4:

$$\begin{aligned} (V_{FG} - V_{REF}) &= V_{DM} \\ V_{OUT} &= V_{DM}G_{DM} + V_{REF} \end{aligned}$$

For an ideal part, changing V_{CM}, V_{SS} or V_{DD} produces no change in V_{OUT}. V_{REF} shifts V_{OUT} as needed.

The different G_{MIN} options change G_{M1}, G_{M2} and the internal compensation capacitor. This results in the performance trade-offs shown in Table 1.

4.1.3 DC ERRORS

Section 1.5 "Explanation of DC Error Specs" defines some of the DC error specifications. These errors are internal to the INA, and can be summarized as follows:

EQUATION 4-5:

$$V_{OUT} = V_{REF} + G_{DM}(1 + g_E)(V_{DM} + \Delta V_{ED}) + G_{DM}(1 + g_E)(V_E + \Delta V_E)$$

Where:

$$V_E = V_{OS} + \frac{\Delta V_{DD} - \Delta V_{SS}}{PSRR} + \frac{\Delta V_{CM}}{CMRR} + \frac{\Delta V_{REF}}{CMRR} + \frac{\Delta V_{OUT}}{A_{OL}} + \Delta T_A \cdot \frac{\Delta V_{OS}}{\Delta T_A}$$

$$\Delta V_{ED} \le INL_{DM}(V_{DMH} - V_{DML})$$

$$\Delta V_E \le INL_{CM}(V_{IVH} - V_{IVL})$$

Where:

PSRR, *CMRR* and A_{OL} are in units of V/V

ΔT_A is in units of °C

The non-linearity specs (INL_{CM} and INL_{DM}) describe errors that are non-linear functions of V_{CM} and V_{DM}, respectively. They give the maximum excursion from linear response over the entire common mode and differential ranges.

The input bias current and offset current specs (I_B and I_{OS}), together with a circuit's external input resistances, give an additional DC error. Figure 4-3 shows the resistors that set the DC bias point.

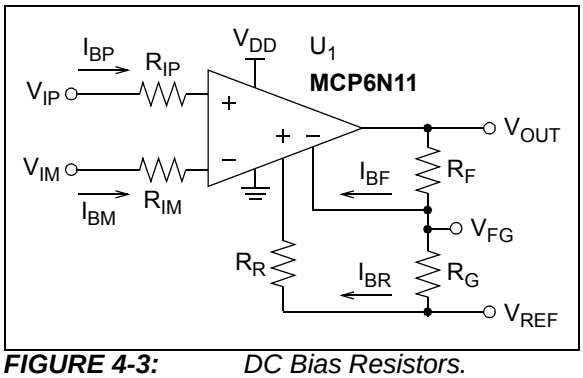


FIGURE 4-3: *DC Bias Resistors.*

The resistors at the main input (R_{IP} and R_{IM}) and its input bias currents (I_{BP} and I_{BM}) give the following changes in the INA's bias voltages:

EQUATION 4-6:

$$\Delta V_{IP} = -I_{BP}R_{IP} = \left(-I_B - \frac{I_{OS}}{2}\right)R_{IP}$$

$$\Delta V_{IM} = -I_{BM}R_{IM} = \left(-I_B + \frac{I_{OS}}{2}\right)R_{IM}$$

$$\Delta V_{CM} = \frac{\Delta V_{IP} + \Delta V_{IM}}{2} = -I_B\left(\frac{R_{IP} + R_{IM}}{2}\right) + \frac{-I_{OS}}{2}\left(\frac{-R_{IP} + R_{IM}}{2}\right)$$

$$\Delta V_{DM} = \Delta V_{IP} - \Delta V_{IM} = I_B(-R_{IP} + R_{IM}) - \frac{I_{OS}}{2}(R_{IP} + R_{IM})$$

$$\Delta V_{OUT} = G_{DM}\left(\Delta V_{DM} + \frac{\Delta V_{CM}}{CMRR}\right)$$

Where:

CMRR is in units of V/V

The best design results when R_{IP} and R_{IM} are equal and small:

EQUATION 4-7:

$$\Delta V_{OUT} \approx G_{DM}\Delta V_{DM} \approx G_{DM}(\pm 2 I_B \varepsilon_{RTOL} - I_{OS})R_{IP}$$

Where:

$R_{IP} = R_{IM}$

ε_{RTOL} = tolerance of R_{IP} and R_{IM}

The resistors at the feedback input (R_R, R_F and R_G) and its input bias currents (I_{BR} and I_{BF}) give the following changes in the INA's bias voltages:

EQUATION 4-8:

$$\Delta V_{REF} = -I_{BR}R_R = \left(-I_{B2} - \frac{I_{OS2}}{2}\right)R_R$$

$\Delta V_{FG} \approx \Delta V_{REF}$, due to high A_{OL}

$$\Delta V_{OUT} \approx I_{B2}(R_F - G_{DM}R_R) + \frac{I_{OS2}}{2}(R_F + G_{DM}R_R)$$

Where:

I_{B2} meets the I_B spec, but is not equal to I_B

I_{OS2} meets the I_{OS} spec, but is not equal to I_{OS}

The best design results when $G_{DM}R_R$ and R_F are equal and small:

EQUATION 4-9:

$$\Delta V_{OUT} \approx (\pm(2 I_{B2} \varepsilon_{RTOL} + I_{OS2}))R_F$$

Where:

$G_{DM}R_R = R_F$

ε_{RTOL} = tolerance of R_R, R_F and R_G

4.1.4 AC PERFORMANCE

The bandwidth of these amplifiers depends on G_{DM} and G_{MIN}:

EQUATION 4-10:

$$f_{BW} \approx \frac{f_{GBWP}}{G_{DM}}$$
$$\approx (0.50\ MHz)(G_{MIN} / G_{DM}), \quad G_{MIN} = 1, \ldots, 10$$
$$\approx (0.35\ MHz)(G_{MIN} / G_{DM}), \quad G_{MIN} = 100$$

Where:

f_{BW} = -3 dB bandwidth

f_{GBWP} = Gain bandwidth product

The bandwidth at the maximum output swing is called the Full Power Bandwidth (f_{FPBW}). It is limited by the Slew Rate (SR) for many amplifiers, but is close to f_{BW} for these parts:

EQUATION 4-11:

$$f_{FPBW} \approx \frac{SR}{\pi V_O}$$
$$\approx f_{BW}, \quad \text{for these parts}$$

Where:

V_O = Maximum output voltage swing

$\approx V_{OH} - V_{OL}$

CMRR is constant from DC to about 1 kHz.

4.1.5 NOISE PERFORMANCE

As shown in Figures 2-41 and 2-42, the 1/f noise causes an apparent wander in the DC output voltage. Changing the measurement time or bandwidth has little effect on this noise.

We recommend re-calibrating V_{OS} periodically, to reduce 1/f noise wander. For example, V_{OS} could be re-calibrated at least once every 15 minutes; more often when temperature or V_{DD} change significantly.

4.2 Functional Blocks

4.2.1 RAIL-TO-RAIL INPUTS

Each input stage uses one PMOS differential pair at the input. The output of each differential pair is processed using current mode circuitry. The inputs show no crossover distortion vs. common mode voltage.

With this topology, the inputs (V_{IP} and V_{IM}) operate normally down to V_{SS} – 0.2V and up to V_{DD} + 0.15V at room temperature (see Figure 2-11). The input offset voltage (V_{OS}) is measured at $V_{CM} = V_{SS}$ – 0.2V and V_{DD} + 0.15V (at +25°C), to ensure proper operation.

4.2.1.1 Phase Reversal

The input devices are designed to not exhibit phase inversion when the input pins exceed the supply voltages. Figures 2-18 and 2-50 show an input voltage exceeding both supplies with no phase inversion.

The input devices also do not exhibit phase inversion when the differential input voltage exceeds its limits; see Figures 2-22 and 2-51.

4.2.1.2 Input Voltage Limits

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the voltages at the input pins (see **Section 1.1 "Absolute Maximum Ratings †"**). This requirement is independent of the current limits discussed later on.

The ESD protection on the inputs can be depicted as shown in Figure 4-4. This structure was chosen to protect the input transistors against many (but not all) overvoltage conditions, and to minimize input bias current (I_B).

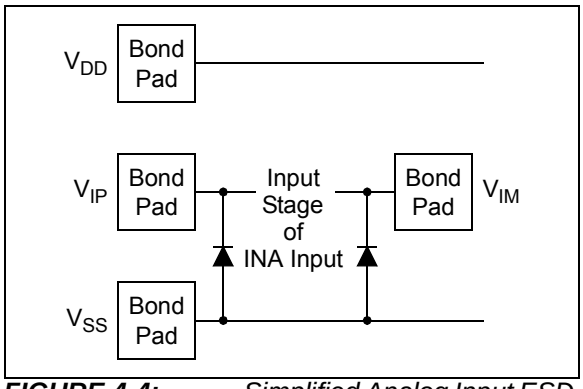


FIGURE 4-4: *Simplified Analog Input ESD Structures.*

The input ESD diodes clamp the inputs when they try to go more than one diode drop below V_{SS}. They also clamp any voltages that go too far above V_{DD}; their breakdown voltage is high enough to allow normal operation, but not low enough to protect against slow overvoltage (beyond V_{DD}) events. Very fast ESD events (that meet the spec) are limited so that damage does not occur.

In some applications, it may be necessary to prevent excessive voltages from reaching the op amp inputs. Figure 4-5 shows one approach to protecting these inputs. D_1 and D_2 may be small signal silicon diodes, Schottky diodes for lower clamping voltages or diode-connected FETs for low leakage.

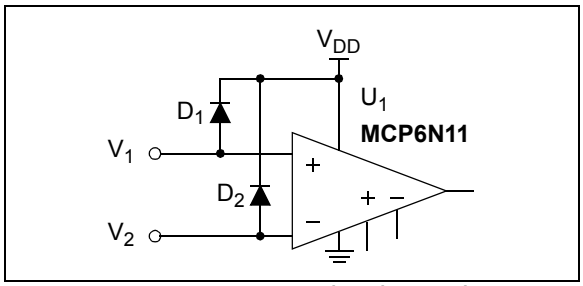


FIGURE 4-5: *Protecting the Analog Inputs Against High Voltages.*

4.2.1.3 Input Current Limits

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the currents into the input pins (see **Section 1.1 "Absolute Maximum Ratings †"**). This requirement is independent of the voltage limits previously discussed.

Figure 4-6 shows one approach to protecting these inputs. The resistors R_1 and R_2 limit the possible current in or out of the input pins (and into D_1 and D_2). The diode currents will dump onto V_{DD}.

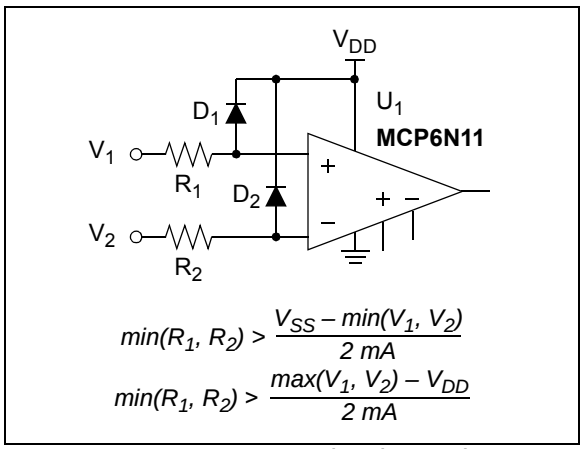


FIGURE 4-6: *Protecting the Analog Inputs Against High Currents.*

It is also possible to connect the diodes to the left of the resistor R_1 and R_2. In this case, the currents through the diodes D_1 and D_2 need to be limited by some other mechanism. The resistors then serve as in-rush current limiters; the DC current into the input pins (V_{IP} and V_{IM}) should be very small.

A significant amount of current can flow out of the inputs (through the ESD diodes) when the common mode voltage (V_{CM}) is below ground (V_{SS}); see Figure 2-25.

4.2.1.4 Input Voltage Ranges

Figure 4-7 shows possible input voltage values (V_{SS} = 0V). Lines with a slope of +1 have constant V_{DM} (e.g., the V_{DM} = 0 line). Lines with a slope of -1 have constant V_{CM} (e.g., the $V_{CM} = V_{DD}/2$ line).

For normal operation, V_{IP} and V_{IM} must be kept within the region surrounded by the thick blue lines. The horizontal and vertical blue lines show the limits on the individual inputs. The blue lines with a slope of +1 show the limits on V_{DM}; the larger G_{MIN} is, the closer they are to the V_{DM} = 0 line.

The input voltage range specs (V_{IVL} and V_{IVH}) change with the supply voltages (V_{SS} and V_{DD}, respectively). The differential input range specs (V_{DML} and V_{DMH}) change with minimum gain (G_{MIN}). Temperature also affects these specs.

To take full advantage of V_{DML} and V_{DMH}, set V_{REF} (see Figure 1-6 and Figure 1-7) so that the output (V_{OUT}) is centered between the supplies (V_{SS} and V_{DD}).

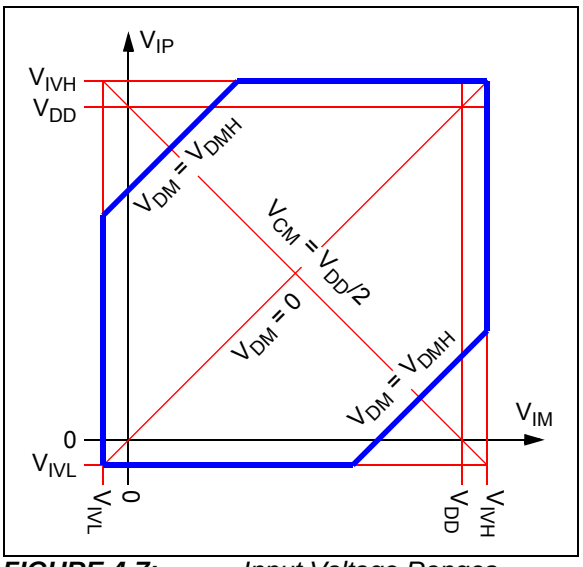


FIGURE 4-7: *Input Voltage Ranges.*

4.2.2 ENABLE/V_{OS} CALIBRATION (EN/$\overline{CAL}$)

These parts have a Normal mode, a Low Power mode and a V_{OS} Calibration mode.

When the EN/$\overline{CAL}$ pin is high and the internal POR (with delay) indicates that power is good, the part operates in its Normal mode.

When the EN/$\overline{CAL}$ pin is low, the part operates in its Low Power mode. The quiescent current (at V_{SS}) drops to -2.5 µA (typical), the amplifier output is put into a high-impedance state. Signals at the input pins can feed through to the output pin.

When the EN/$\overline{CAL}$ pin goes high and the internal POR (with delay) indicates that power is good, the amplifier internally corrects its input offset voltage (V_{OS}) with the internal common mode voltage at mid-supply ($V_{DD}/2$) and the output tri-stated (after t_{OFF}). Once V_{OS} Calibration is completed, the amplifier is enabled and normal operation resumes.

The EN/$\overline{CAL}$ pin does not operate normally when left floating. Either drive it with a logic output, or tie it high so that the part is always on.

4.2.3 POR WITH DELAY

The internal POR makes sure that the input offset voltage (V_{OS}) is calibrated whenever the supply voltage goes from low voltage (< V_{PRL}) to high voltage (> V_{PRH}). This prevents corruption of the V_{OS} trim registers after a low-power event.

After the POR goes high, the internal circuitry adds a fixed delay (t_{PLH}), before telling the V_{OS} Calibration circuitry (see Figure 4-2) to start. If the EN/$\overline{CAL}$ pin is toggled during this time, the fixed delay is restarted (takes an additional time t_{PLH}).

4.2.4 PARITY DETECTOR

A parity error detector monitors the memory contents for any corruption. In the rare event that a parity error is detected (e.g., corruption from an alpha particle), a POR event is automatically triggered. This will cause the input offset voltage to be re-corrected, and the op amp will not return to normal operation for a period of time (the POR turn on time, t_{PLH}).

4.2.5 RAIL-TO-RAIL OUTPUT

The Minimum Output Voltage (V_{OL}) and Maximum Output Voltage (V_{OH}) specs describe the widest output swing that can be achieved under the specified load conditions.

The output can also be limited when V_{IP} or V_{IM} exceeds V_{IVL} or V_{IVH}, or when V_{DM} exceeds V_{DML} or V_{DMH}.

4.3 Applications Tips

4.3.1 MINIMUM STABLE GAIN

There are different options for different Minimum Stable Gains (1, 2, 5, 10 and 100 V/V; see Table 1-1). The differential gain (G_{DM}) needs to be greater than or equal to G_{MIN} in order to maintain stability.

Picking a part with higher G_{MIN} has the advantages of lower Input Noise Voltage Density (e_{ni}), lower Input Offset Voltage (V_{OS}) and increased Gain Bandwidth Product (GBWP); see Table 1. The Differential Input Voltage Range (V_{DMR}) is lower for higher G_{MIN}, but the output voltage range would limit V_{DMR} anyway, when $G_{DM} \geq 2$.

4.3.2 CAPACITIVE LOADS

Driving large capacitive loads can cause stability problems for amplifiers. As the load capacitance increases, the feedback loop's phase margin decreases, and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. Lower gains (G_{DM}) exhibit greater sensitivity to capacitive loads.

When driving large capacitive loads with these instrumentation amps (e.g., > 100 pF), a small series resistor at the output (R_{ISO} in Figure 4-8) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitive load.

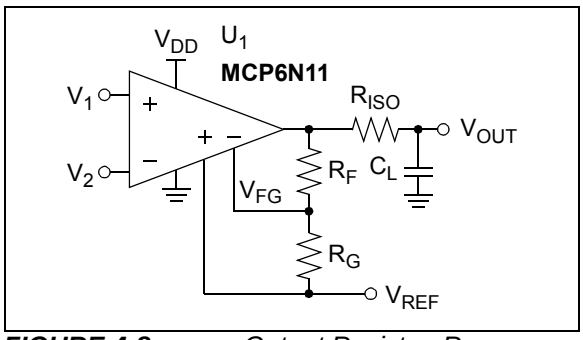


FIGURE 4-8: *Output Resistor, R_{ISO} stabilizes large capacitive loads.*

Figure 4-9 gives recommended R_{ISO} values for different capacitive loads and gains. The x-axis is the normalized load capacitance (C_L G_{MIN}/G_{DM}), where G_{DM} is the circuit's differential gain ($1 + R_F / R_G$) and G_{MIN} is the minimum stable gain.

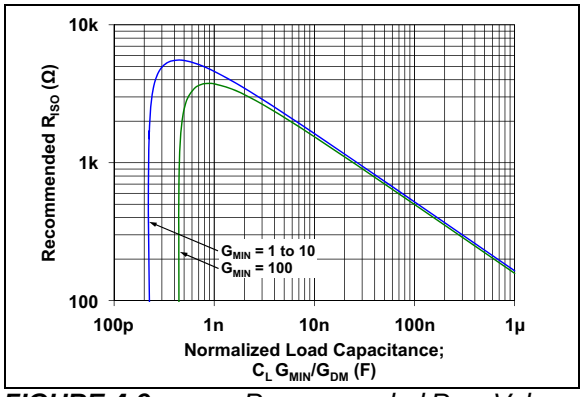


FIGURE 4-9: *Recommended R_{ISO} Values for Capacitive Loads.*

After selecting R_{ISO} for your circuit, double check the resulting frequency response peaking and step response overshoot on the bench. Modify R_{ISO}'s value until the response is reasonable.

4.3.3 GAIN RESISTORS

Figure 4-10 shows a simple gain circuit with the INA's input capacitances at the feedback inputs (V_{REF} and V_{FG}). These capacitances interact with R_G and R_F to modify the gain at high frequencies. The equivalent capacitance acting in parallel to R_G is $C_G = C_{DM} + C_{CM}$ plus any board capacitance in parallel to R_G. C_G will cause an increase in G_{DM} at high frequencies, which reduces the phase margin of the feedback loop (i.e., reduce the feedback loop's stability).

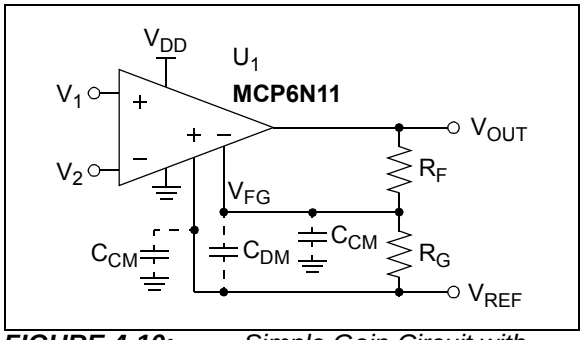


FIGURE 4-10: *Simple Gain Circuit with Parasitic Capacitances.*

In this data sheet, $R_F + R_G = 10\ k\Omega$ for most gains (0Ω for $G_{DM} = 1$); see Table 1-6. This choice gives good Phase Margin. In general, R_F (Figure 4-10) needs to meet the following limits to maintain stability:

EQUATION 4-12:

For G_{DM} = 1:

$$R_F = 0$$

For G_{DM} > 1:

$$R_F < \frac{\alpha G_{DM}^2}{2\pi f_{GBWP} C_G}$$

Where:

$\alpha \leq 0.25$

$G_{DM} \geq G_{MIN}$

f_{GBWP} = Gain Bandwidth Product

$C_G = C_{DM} + C_{CM}$ + (PCB stray capacitance)

4.3.4 SUPPLY BYPASS

With these INAs, the power supply pin (V_{DD} for single supply) should have a local bypass capacitor (i.e., 0.01 µF to 0.1 µF) within 2 mm for good high frequency performance. Surface mount, multilayer ceramic capacitors, or their equivalent, should be used.

These INAs require a bulk capacitor (i.e., 1.0 µF or larger) within 100 mm, to provide large, slow currents. This bulk capacitor can be shared with other nearby analog parts as long as crosstalk through the supplies does not prove to be a problem.

4.4 Typical Applications

4.4.1 HIGH INPUT IMPEDANCE DIFFERENCE AMPLIFIER

Figure 4-11 shows the MCP6N11 used as a difference amplifier. The inputs are high impedance and give good CMRR performance.

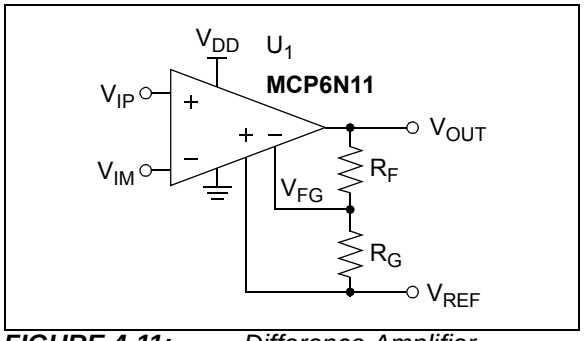


FIGURE 4-11: *Difference Amplifier.*

4.4.2 DIFFERENCE AMPLIFIER FOR VERY LARGE COMMON MODE SIGNALS

Figure 4-12 shows the MCP6N11 INA used as a difference amplifier for signals with a very large common mode component. The input resistor dividers (R_1 and R_2) ensure that the voltages at the INA's inputs are within their range of normal operation. The capacitors C_1, with the parasitic capacitances C_2 (the resistors' parasitic capacitance plus the INA's input common mode capacitance, C_{CM}), set the same division ratio, so that high-frequency signals (e.g., a step in voltage) have the same gain. Select the INA gain to compensate for R_1 and R_2's attenuation. Select R_1 and R_2's tolerances for good CMRR.

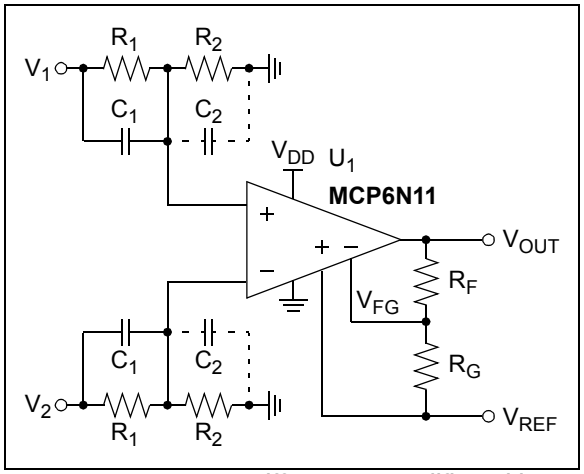
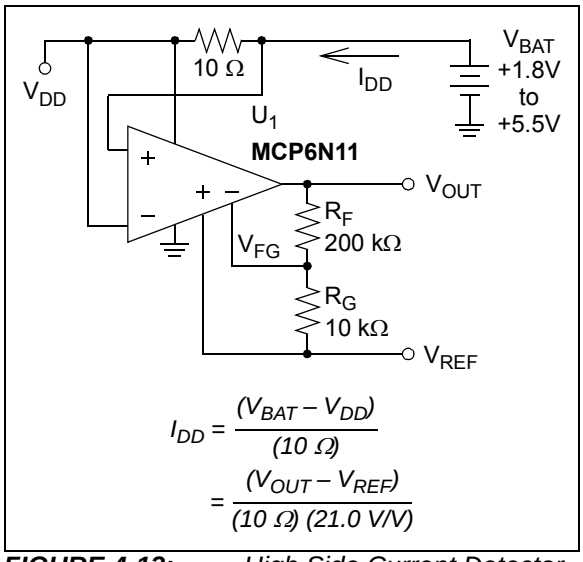


FIGURE 4-12: *Difference Amplifier with Very Large Common Mode Component.*

4.4.3 HIGH SIDE CURRENT DETECTOR

Figure 4-13 shows the MCP6N11 INA used as to detect and amplify the high side current in a battery powered design. The INA gain is set at 21 V/V, so V_{OUT} changes 210 mV for every 1 mA of I_{DD} current. The best G_{MIN} option to pick would be a gain of 10 (MCP6N11-010).



$$I_{DD} = \frac{(V_{BAT} - V_{DD})}{(10\ \Omega)} = \frac{(V_{OUT} - V_{REF})}{(10\ \Omega)\ (21.0\ V/V)}$$

FIGURE 4-13: *High Side Current Detector.*

4.4.4 WHEATSTONE BRIDGE

Figure 4-14 shows the MCP6N11 single instrumentation amp used to condition the signal from a Wheatstone bridge (e.g., strain gage). The overall INA gain is set at 201 V/V. The best G_{MIN} option to pick, for this gain, is 100 V/V (MCP6N11-100).

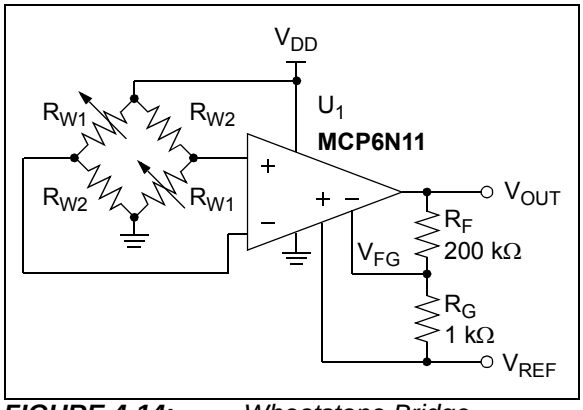


FIGURE 4-14: *Wheatstone Bridge Amplifier.*

NOTES:

5.0 DESIGN AIDS

Microchip provides the basic design aids needed for the MCP6N11 instrumentation amplifiers.

5.1 Microchip Advanced Part Selector (MAPS)

MAPS is a software tool that helps efficiently identify Microchip devices that fit a particular design requirement. Available at no cost from the Microchip website at www.microchip.com/maps, the MAPS is an overall selection tool for Microchip's product portfolio that includes Analog, Memory, MCUs and DSCs. Using this tool, a customer can define a filter to sort features for a parametric search of devices and export side-by-side technical comparison reports. Helpful links are also provided for Data sheets, Purchase and Sampling of Microchip parts.

5.2 Analog Demonstration Board

Microchip offers a broad spectrum of Analog Demonstration and Evaluation Boards that are designed to help customers achieve faster time to market. For a complete listing of these boards and their corresponding user's guides and technical information, visit the Microchip web site at www.microchip.com/analog tools.

5.3 Application Notes

The following Microchip Application Notes are available on the Microchip web site at www.microchip.com/appnotes and are recommended as supplemental reference resources.

- **AN884:** *"Driving Capacitive Loads With Op Amps"*, DS00884
- **AN990:** *"Analog Sensor Conditioning Circuits – An Overview"*, DS00990
- **AN1228:** *"Op Amp Precision Design: Random Noise"*, DS01228

Some of these application notes, and others, are listed in the design guide:

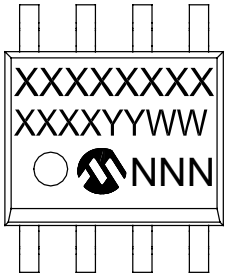
- *"Signal Chain Design Guide"*, DS21825

NOTES:

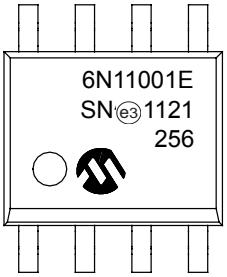
6.0 PACKAGING INFORMATION

6.1 Package Marking Information

8-Lead SOIC (150 mil) **(MCP6N11)**



Example



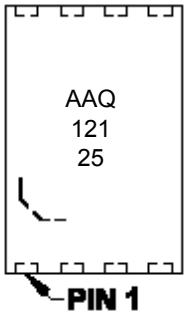
Note: The example is for a MCP6N11-001 part.

8-Lead TDFN (2×3) **(MCP6N11)**

Device	Code
MCP6N11-001	AAQ
MCP6N11-002	AAR
MCP6N11-005	AAS
MCP6N11-010	AAT
MCP6N11-100	AAU

Note: Applies to 8-Lead 2x3 TDFN

Example

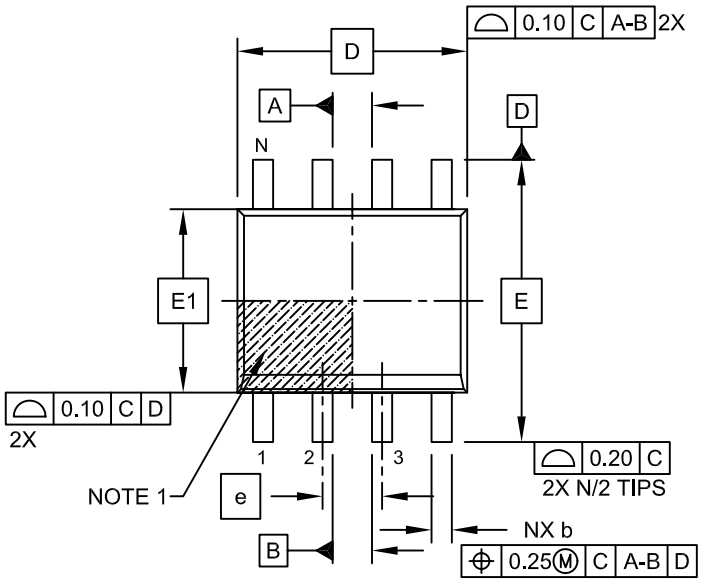


Legend:	XX...X	Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week ‘01’)
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.

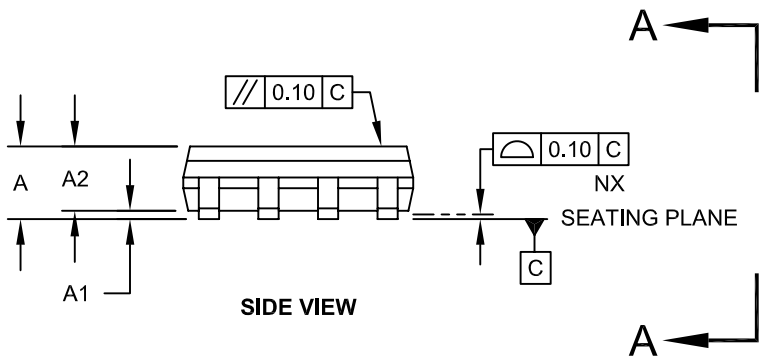
Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

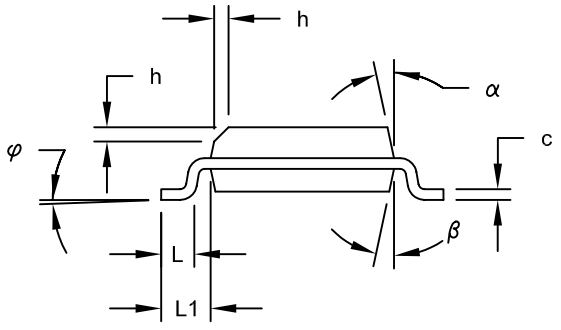
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



TOP VIEW



SIDE VIEW

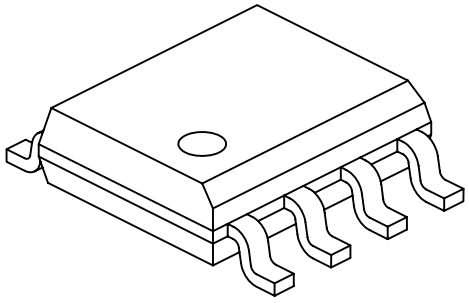


VIEW A-A

Microchip Technology Drawing No. C04-057C Sheet 1 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e		1.27 BSC	
Overall Height	A	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E		6.00 BSC	
Molded Package Width	E1		3.90 BSC	
Overall Length	D		4.90 BSC	
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40	-	1.27
Footprint	L1		1.04 REF	
Foot Angle	φ	0°	-	8°
Lead Thickness	c	0.17	-	0.25
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5°	-	15°

Notes:

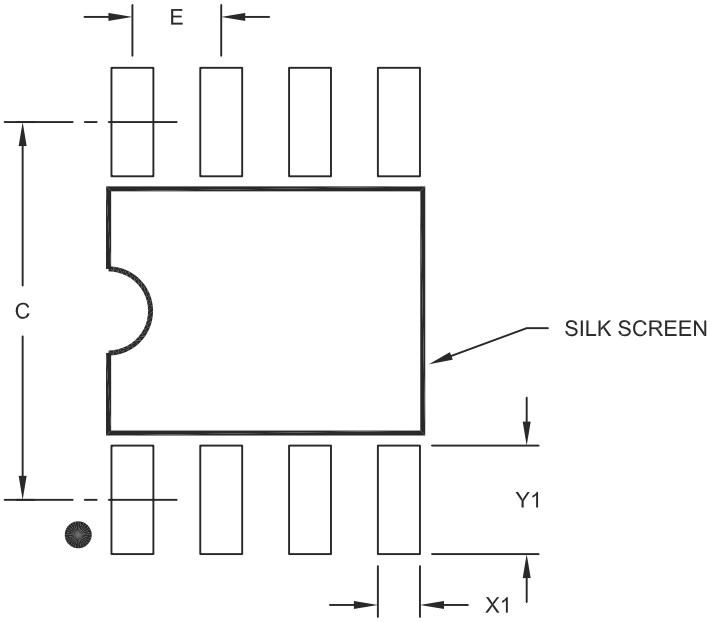
1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. § Significant Characteristic
3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.
REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	C		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

Notes:

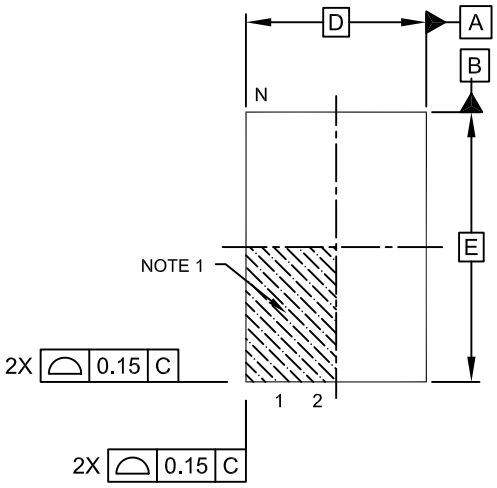
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

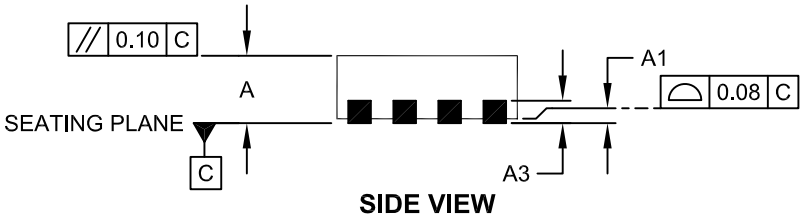
Microchip Technology Drawing No. C04-2057A

8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75mm Body [TDFN]

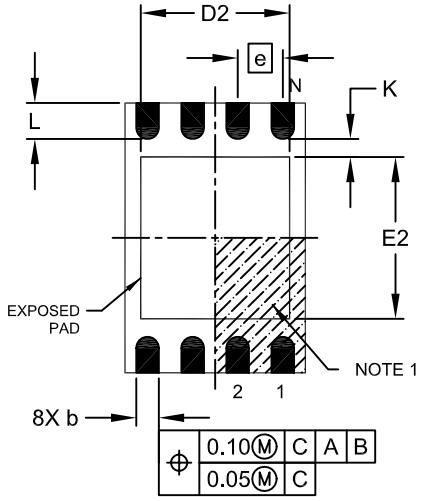
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



TOP VIEW



SIDE VIEW

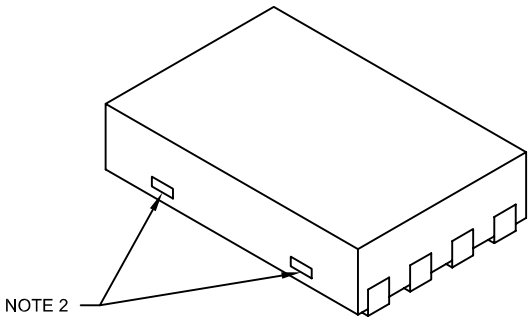


BOTTOM VIEW

Microchip Technology Drawing No. C04-129C Sheet 1 of 2

8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75mm Body [TDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e		0.50 BSC	
Overall Height	A	0.70	0.75	0.80
Standoff	A1	0.00	0.02	0.05
Contact Thickness	A3		0.20 REF	
Overall Length	D		2.00 BSC	
Overall Width	E		3.00 BSC	
Exposed Pad Length	D2	1.20	-	1.60
Exposed Pad Width	E2	1.20	-	1.60
Contact Width	b	0.20	0.25	0.30
Contact Length	L	0.25	0.30	0.45
Contact-to-Exposed Pad	K	0.20	-	-

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. Package may have one or more exposed tie bars at ends.
3. Package is saw singulated
4. Dimensioning and tolerancing per ASME Y14.5M

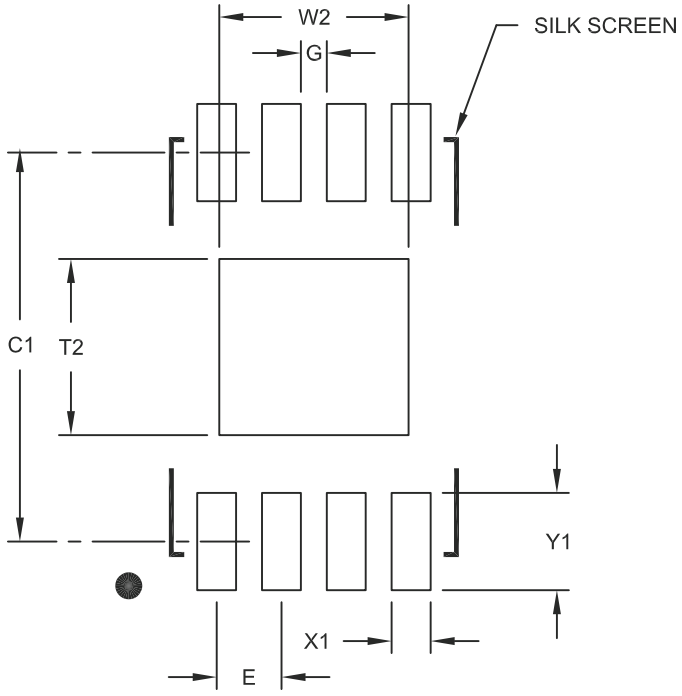
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-129C Sheet 2 of 2

8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75 mm Body [TDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E		0.50 BSC	
Optional Center Pad Width	W2			1.46
Optional Center Pad Length	T2			1.36
Contact Pad Spacing	C1		3.00	
Contact Pad Width (X8)	X1			0.30
Contact Pad Length (X8)	Y1			0.75
Distance Between Pads	G	0.20		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2129A

NOTES:

APPENDIX A: REVISION HISTORY

Revision A (October 2011)

- Original Release of this Document.

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	–X	X	/XX
Device	Gain Option	Temperature Range	Package

Device:	MCP6N11	Single Instrumentation Amplifier
	MCP6N11T	Single Instrumentation Amplifier (Tape and Reel)
Gain Option:	001 =	Minimum gain of 1 V/V
	002 =	Minimum gain of 2 V/V
	005 =	Minimum gain of 5 V/V
	010 =	Minimum gain of 10 V/V
	100 =	Minimum gain of 100 V/V
Temperature Range:	E =	-40°C to +125°C
Package:	MNY =	2×3 TDFN, 8-lead *
	SN =	Plastic SOIC (150mil Body), 8-lead

* Y = nickel palladium gold manufacturing designator. Only available on the TDFN package.

Examples:

a) MCP6N11T-001E/MNY: Tape and Reel, Minimum gain = 1, Extended temperature, 8LD 2×3 TDFN.

b) MCP6N11-002E/SN: Minimum gain = 2, Extended temperature, 8LD SOIC.

NOTES:

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- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
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- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

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